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### Electronic devices including support pillars in slot regions, and related memory devices, systems, and methods

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#### Abstract

An electronic device comprises a stack comprising tiers of alternating conductive levels and insulative levels overlying a source, slots extending vertically through the stack and dividing the stack into blocks, and support pillars within the slots and extending vertically through the stack. The support pillars exhibit a lateral dimension in a first horizontal direction relatively larger than a lateral dimension of the slots in the first horizontal direction, substantially orthogonal to a second horizontal direction in which the slots extend. Related memory devices, systems, and methods are also described.

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## Background/Summary

## TECHNICAL FIELD

(1) Embodiments disclosed herein relate to the field of electronic device design and fabrication. More particularly, embodiments of the disclosure relate to electronic devices including pillars (e.g., memory cell pillars) within pillar array regions and support pillars within slot regions between pillar array blocks, and to related memory devices, systems, and methods of forming the electronic devices.

## BACKGROUND

(2) A continuing goal of the electronics industry has been to increase the memory density (e.g., the number of memory cells per memory die) of memory devices, such as non-volatile memory devices (e.g., NAND Flash memory devices). One way of increasing memory density in non-volatile memory devices is to utilize vertical memory array (also referred to as a “three-dimensional (3D) memory array”) architectures. A conventional vertical memory array includes vertical memory strings extending through openings in one or more stack structures including tiers of conductive structures and insulative structures. Each vertical memory string may include at least one select device coupled in series to a serial combination of vertically-stacked memory cells. Such a configuration permits a greater number of switching devices (e.g., transistors) to be located in a unit of die area (i.e., length and width of active surface consumed) by building the array upwards (e.g., vertically) on a die, as compared to structures with conventional planar (e.g., two-dimensional) arrangements of transistors.

(3) Vertical memory array architectures generally include electrical connections between the conductive structures of the tiers of the stack structure(s) of the memory device and access lines (e.g., word lines) so that the memory cells of the vertical memory array can be uniquely selected for writing, reading, or erasing operations. One method of forming such an electrical connection includes forming so-called “staircase” (or “stair step”) structures at edges (e.g., horizontal ends) of the conductive structures of the stack structure(s) of the memory device. The staircase structure includes individual “steps” defining contact regions of the conductive structures, upon which conductive contact structures can be positioned to provide electrical access to the conductive structures.

(4) As vertical memory array technology has advanced, additional memory density has been provided by forming vertical memory arrays to include stacks comprising additional tiers of conductive structures and, hence, additional staircase structures and/or additional steps in individual staircase structures associated therewith. As the height of the stacks increases to facilitate additional memory cells in the vertical memory arrays, the stacks may be prone to toppling or collapse during subsequently-conducted processing acts. For example, during replacement gate processing acts, the stacks may be subject to tier collapse during or after removal of portions of the tiers to be replaced with the conductive structures. Collapse of the portions of the stacks may reduce reliability of the vertical memory strings.

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## Description

### BRIEF DESCRIPTION OF THE DRAWINGS

(1) FIGS. 1A through 1P are simplified partial cross-sectional (FIGS. 1A, 1C-1E, 1G-1I, 1K-1N, and 1P) and simplified partial top-down (FIGS. 1, 1F, 1J, and 1O) views illustrating a method of forming an electronic device, in accordance with embodiments of the disclosure, where the top-down views of FIGS. 1B, 1F, 1J, and 1O are taken along the A-A line, the E-E line, the I-I line, and the N-N line in FIGS. 1A, 1E, 1I, and 1N, respectively;

(2) FIG. 2 is a partial cutaway perspective view of an electronic device, in accordance with embodiments of the disclosure;

(3) FIG. 3 is a block diagram of a system, in accordance with embodiments of the disclosure; and

(4) FIG. 4 is a block diagram of a processor-based system, in accordance with embodiments of the disclosure.

#### DETAILED DESCRIPTION

(5) An electronic device (e.g., an apparatus, a semiconductor device, a memory device) that includes support pillars (e.g., active support pillars) within slot regions between pillar array blocks is disclosed. The electronic device comprises a stack comprising tiers of alternating conductive levels (e.g., conductive structures) and insulative levels (e.g., insulative structures) overlying a source. Slots, which may also be referred to as “slits” or “replacement gate slots” extend vertically through the stack and divide the stack into blocks. The support pillars are located within the slots and extend vertically through the stack. The support pillars exhibit a lateral dimension (e.g., a width) in a first horizontal direction that is relatively larger than a lateral dimension of the slots in the first horizontal direction, substantially orthogonal to a second horizontal direction in which the slots extend. The electronic device may include a barrier material (e.g., a carbon-containing material) within the slots and laterally separating the support pillars from one another. A single line of the support pillars extends in the second horizontal direction within the slots. For example, the barrier material may be formed within the slots prior to conducting replacement gate processing acts, which processing acts may be conducted through support pillar openings in the barrier material. Portions of the barrier material may remain within the slots during such processing acts to provide structural support to the stack during formation of conductive structures of the conductive levels. In some embodiments, the insulative levels of the stack include one or more air gaps vertically separating the conductive structures from one another.

(6) The support pillars, in combination with the barrier material, within the slots may provide increased structural support at locations horizontally proximate to the horizontal ends (e.g., horizontal boundaries) of large cantilever structures of the insulative structures of the tiers during the formation of the conductive structures. The support pillars and the barrier material may also provide structural support to the conductive structures to facilitate formation of the air gaps. By providing the portions of the barrier material that remain within the slots during formation of the conductive structures and the air gaps, such configurations may, for example, reduce or substantially prevent undesirable tier deformations (e.g., tier warping) and/or tier collapse during the formation of the conductive structures and the air gaps. Such a configuration may reduce or substantially prevent the risk of undesirable current leakage and short circuits during use and operation of the electronic device without significantly affecting conductivity.

(7) The following description provides specific details, such as material compositions, shapes, and sizes, in order to provide a thorough description of embodiments of the disclosure. However, a person of ordinary skill in the art would understand that the embodiments of the disclosure may be practiced without employing these specific details. Indeed, the embodiments of the disclosure may be practiced in conjunction with conventional electronic device fabrication techniques employed in the industry. In addition, the description provided below does not form a complete process flow for manufacturing an electronic device (e.g., a memory device, such as 3D NAND Flash memory device). The structures described below do not form a complete electronic device. Only those process acts and structures necessary to understand the embodiments of the disclosure are described in detail below. Additional acts to form a complete electronic device from the structures may be performed by conventional fabrication techniques.

(8) Unless otherwise indicated, the materials described herein may be formed by conventional techniques including, but not limited to, spin coating, blanket coating, chemical vapor deposition (CVD), atomic layer deposition (ALD), plasma enhanced ALD, physical vapor deposition (PVD) (including sputtering, evaporation, ionized PVD, and/or plasma-enhanced CVD), or epitaxial growth. Alternatively, the materials may be grown in situ. Depending on the specific material to be formed, the technique for depositing or growing the material may be selected by a person of ordinary skill in the art. The removal of materials may be accomplished by any suitable technique

including, but not limited to, etching (e.g., dry etching, wet etching, vapor etching), ion milling, abrasive planarization (e.g., chemical-mechanical planarization), or other known methods unless the context indicates otherwise.

(9) Drawings presented herein are for illustrative purposes only, and are not meant to be actual views of any particular material, component, structure, electronic device, or electronic system. Variations from the shapes depicted in the drawings as a result, for example, of manufacturing techniques and/or tolerances, are to be expected. Thus, embodiments described herein are not to be construed as being limited to the particular shapes or regions as illustrated, but include deviations in shapes that result, for example, from manufacturing. For example, a region illustrated or described as box-shaped may have rough and/or nonlinear features, and a region illustrated or described as round may include some rough and/or linear features. Moreover, sharp angles that are illustrated may be rounded, and vice versa. Thus, the regions illustrated in the figures are schematic in nature, and their shapes are not intended to illustrate the precise shape of a region and do not limit the scope of the present claims. The drawings are not necessarily to scale. Additionally, elements common between figures may retain the same numerical designation.

(10) As used herein, the singular forms “a,” “an,” and “the” are intended to include the plural forms as well, unless the context clearly indicates otherwise.

(11) As used herein, “and/or” includes any and all combinations of one or more of the associated listed items.

(12) As used herein, spatially relative terms, such as “beneath,” “below,” “lower,” “bottom,” “above,” “upper,” “top,” “front,” “rear,” “left,” “right,” and the like, may be used for ease of description to describe one element's or feature's relationship to another element(s) or feature(s) as illustrated in the figures. Unless otherwise specified, the spatially relative terms are intended to encompass different orientations of the materials in addition to the orientation depicted in the figures. For example, if materials in the figures are inverted, elements described as “below” or “beneath” or “under” or “on bottom of” other elements or features would then be oriented “above” or “on top of” the other elements or features. Thus, the term “below” can encompass both an orientation of above and below, depending on the context in which the term is used, which will be evident to one of ordinary skill in the art. The materials may be otherwise oriented (e.g., rotated 90 degrees, inverted, flipped) and the spatially relative descriptors used herein interpreted accordingly.

(13) As used herein, the terms “vertical,” “longitudinal,” “horizontal,” and “lateral” are in reference to a major plane of a structure and are not necessarily defined by Earth's gravitational field. A “horizontal” or “lateral” direction is a direction that is substantially parallel to the major plane of the structure, while a “vertical” or “longitudinal” direction is a direction that is substantially perpendicular to the major plane of the structure. The major plane of the structure is defined by a surface of the structure having a relatively large area compared to other surfaces of the structure.

(14) As used herein, reference to an element as being “on” or “over” another element means and includes the element being directly on top of, directly adjacent to (e.g., directly laterally adjacent to, directly vertically adjacent to), directly underneath, or in direct contact with the other element. It also includes the element being indirectly on top of, indirectly adjacent to (e.g., indirectly laterally adjacent to, indirectly vertically adjacent to), indirectly underneath, or near the other element, with other elements present therebetween. In contrast, when an element is referred to as being “directly on” or “directly adjacent to” another element, there are no intervening elements present.

(15) As used herein, the term “configured” refers to a size, shape, material composition, and arrangement of one or more of at least one structure and at least one apparatus facilitating operation of one or more of the structure and the apparatus in a pre-determined way.

(16) As used herein, features (e.g., regions, materials, structures, devices) described as “neighboring” one another means and includes features of the disclosed identity (or identities) that are located most proximate (e.g., closest to) one another. Additional features (e.g., additional regions, additional materials, additional structures, additional devices) not matching the disclosed

identity (or identities) of the “neighboring” features may be disposed between the “neighboring” features. Stated another way, the “neighboring” features may be positioned directly adjacent one another, such that no other feature intervenes between the “neighboring” features; or the “neighboring” features may be positioned indirectly adjacent one another, such that at least one feature having an identity other than that associated with at least one the “neighboring” features is positioned between the “neighboring” features. Accordingly, features described as “vertically neighboring” one another means and includes features of the disclosed identity (or identities) that are located most vertically proximate (e.g., vertically closest to) one another. Moreover, features described as “horizontally neighboring” one another means and includes features of the disclosed identity (or identities) that are located most horizontally proximate (e.g., horizontally closest to) one another.

(17) As used herein, the term “substantially” in reference to a given parameter, property, or condition means and includes to a degree that one of ordinary skill in the art would understand that the given parameter, property, or condition is met with a degree of variance, such as within acceptable tolerances. By way of example, depending on the particular parameter, property, or condition that is substantially met, the parameter, property, or condition may be at least 90.0 percent met, at least 95.0 percent met, at least 99.0 percent met, at least 99.9 percent met, or even 100.0 percent met.

(18) As used herein, “about” or “approximately” in reference to a numerical value for a particular parameter is inclusive of the numerical value and a degree of variance from the numerical value that one of ordinary skill in the art would understand is within acceptable tolerances for the particular parameter. For example, “about” or “approximately” in reference to a numerical value may include additional numerical values within a range of from 90.0 percent to 108.0 percent of the numerical value, such as within a range of from 95.0 percent to 105.0 percent of the numerical value, within a range of from 97.5 percent to 102.5 percent of the numerical value, within a range of from 99.0 percent to 101.0 percent of the numerical value, within a range of from 99.5 percent to 100.5 percent of the numerical value, or within a range of from 99.9 percent to 100.1 percent of the numerical value.

(19) As used herein, the term “memory device” means and includes microelectronic devices exhibiting memory functionality, but not necessarily limited to memory functionality. Stated another way, and by way of example only, the term “memory device” means and includes not only conventional memory (e.g., conventional volatile memory, such as conventional dynamic random access memory (DRAM); conventional non-volatile memory, such as conventional NAND memory), but also includes an application specific integrated circuit (ASIC) (e.g., a system on a chip (SoC)), an electronic device combining logic and memory, or a graphics processing unit (GPU) incorporating memory.

(20) As used herein, the term “electronic device” includes, without limitation, a memory device, as well as a semiconductor device which may or may not incorporate memory, such as a logic device, a processor device, or a radiofrequency (RF) device. Further, an electronic device may incorporate memory in addition to other functions such as, for example, a so-called “system on a chip” (SoC) including a processor and memory, or an electronic device including logic and memory. The electronic device may, for example, be a 3D electronic device, such as a 3D NAND Flash memory device.

(21) As used herein, the term “conductive material” means and includes an electrically conductive material. The conductive material may include one or more of a doped polysilicon, undoped polysilicon, a metal, an alloy, a conductive metal oxide, a conductive metal nitride, a conductive metal silicide, and a conductively doped semiconductor material. By way of example only, the conductive material may be one or more of tungsten (W), tungsten nitride (WN.sub.y), nickel (Ni), tantalum (Ta), tantalum nitride (TaN.sub.y), tantalum silicide (TaSi.sub.x), platinum (Pt), copper (Cu), silver (Ag), gold (Au), aluminum (Al), molybdenum (Mo), titanium (Ti), titanium nitride

(TiN.sub.y), titanium silicide (TiSi.sub.x), titanium silicon nitride (TiSi.sub.xN.sub.y), titanium aluminum nitride (TiAl.sub.xN.sub.y), molybdenum nitride (MoN.sub.x), iridium (Ir), iridium oxide (IrO.sub.z), ruthenium (Ru), ruthenium oxide (RuO.sub.z), n-doped polysilicon, p-doped polysilicon, undoped polysilicon, and conductively doped silicon.

(22) As used herein, a “conductive structure” means and includes a structure formed of and including one or more conductive materials.

(23) As used herein, “insulative material” means and includes electrically insulative material, such as one or more of at least one dielectric oxide material (e.g., one or more of a silicon oxide (SiO.sub.x), phosphosilicate glass, borosilicate glass, borophosphosilicate glass, fluorosilicate glass, an aluminum oxide (AlO.sub.x), a hafnium oxide (HfO.sub.x), a niobium oxide (NbO.sub.x), a titanium oxide (TiO.sub.x), a zirconium oxide (ZrO.sub.x), a tantalum oxide (TaO.sub.x), and a magnesium oxide (MgO.sub.x)), at least one dielectric nitride material (e.g., a silicon nitride (SiN.sub.y)), at least one dielectric oxynitride material (e.g., a silicon oxynitride (SiO.sub.xN.sub.y)), and at least one dielectric carboxynitride material (e.g., a silicon carboxynitride (SiO.sub.xC.sub.zN.sub.y)). Formulae including one or more of “x,” “y,” and “z” herein (e.g., SiO.sub.x, AlO.sub.x, HfO.sub.x, NbO.sub.x, TiO.sub.x, SiN.sub.y, SiO.sub.xN.sub.y, SiO.sub.xC.sub.zN.sub.y) represent a material that contains an average ratio of “x” atoms of one element, “y” atoms of another element, and “z” atoms of an additional element (if any) for every one atom of another element (e.g., Si, Al, Hf, Nb, Ti). As the formulae are representative of relative atomic ratios and not strict chemical structure, an insulative material may comprise one or more stoichiometric compounds and/or one or more non-stoichiometric compounds, and values of “x,” “y,” and “z” (if any) may be integers or may be non-integers. As used herein, the term “non-stoichiometric compound” means and includes a chemical compound with an elemental composition that cannot be represented by a ratio of well-defined natural numbers and is in violation of the law of definite proportions.

(24) As used herein, an “insulative structure” means and includes a structure formed of and including one or more insulative materials.

(25) As used herein, the term “selectively etchable” means and includes a material that exhibits a greater etch rate responsive to exposure to a given etch chemistry and/or process conditions relative to another material exposed to the same etch chemistry and/or process conditions. For example, the material may exhibit an etch rate that is at least about five times greater than the etch rate of another material, such as an etch rate of about ten times greater, about twenty times greater, or about forty times greater than the etch rate of the another material. Etch chemistries and etch conditions for selectively etching a desired material may be selected by a person of ordinary skill in the art.

(26) As used herein, the term “sacrificial,” when used in reference to a material or structure, means and includes a material or structure that is formed during a fabrication process but which is removed (e.g., substantially removed) prior to completion of the fabrication process.

(27) As used herein, the term “air gap” means a volume extending into or through another region or material, or between regions or materials, leaving a void in that other region or material, or between regions or materials, that is empty of a solid and/or liquid material. An air gap is not necessarily empty of a gaseous material (e.g., air, oxygen, nitrogen, argon, helium, or a combination thereof) and does not necessarily contain air. An air gap may be, but is not necessarily, a void (e.g., an unfilled volume, a vacuum).

(28) FIGS. 1A through 1P illustrate a method of forming an electronic device (e.g., a memory device, such as a 3D NAND Flash memory device), in accordance with embodiments of the disclosure, of which FIG. 1P is an enlargement of the portion of FIG. 1N indicated by the dashed line of box 172. FIG. 1A is a simplified cross-sectional view of an electronic device 100 taken along the A-A line of FIG. 1B. The electronic device 100 may, for example, be formed into a portion of a memory device, as described in further detail below.

(29) With reference to FIG. 1A, the electronic device **100** may be formed to include a stack **101** (e.g., a preliminary stack) including a vertically (e.g., in the Z-direction) alternating sequence of insulative structures **106** and additional insulative structures **108** arranged in tiers **112**. Each of the tiers **112** may include one of the insulative structures **106** directly vertically adjacent at least one of the additional insulative structures **108**. For convenience in describing FIGS. 1A through 1P, a first direction may be defined as the X-direction and a second direction, which is orthogonal (e.g., perpendicular) to the first direction, as the Y-direction. A third direction, which is orthogonal (e.g., perpendicular) to each of the first direction and the second direction, may be defined as the Z-direction.

(30) The electronic device **100** is formed to include a source **102** underlying a first deck **103** of the stack **101**, a first barrier material **104** separating the source **102** from a lowermost one of the insulative structures **106** of the stack **101**, and a second deck **105** (FIG. 1D) overlying the first deck **103**. The electronic device **100** includes a slot region **107** horizontally neighboring (e.g., in the X-direction) one or more pillar array regions **109** (e.g., memory array regions). As described in further detail below, the electronic device **100** further includes additional components (e.g., features, structures, devices) within boundaries of the different regions. The electronic device **100** is formed to include an etch stop material **114** underlying (e.g., at the bottom of) a first slot **111** within the slot region **107** and an additional etch stop material **115** underlying (e.g., at the bottom of) first pillar openings **110** within the pillar array regions **109**. As described below, the first slot **111** may divide the stack **101** of the electronic device **100** into separate blocks. While FIG. 1A illustrates a single (e.g., only one) first slot **111** within a single slot region **107** horizontally neighboring two of the pillar array regions **109**, additional first slots **111** including subsequently formed structures may be included within additional slot regions **107** separating additional pillar array regions **109** of the electronic device **100**.

(31) A number (e.g., quantity) of the tiers **112** of the stack **101** may be within a range from about 32 of the tiers **112** to about 256 of the tiers **112**. In some embodiments, the stack **101** includes about 128 of the tiers **112**. However, the disclosure is not so limited, and the stack **101** may include a different number of the tiers **112**. The stack **101** may comprise at least one (e.g., one, two, more than two) deck structure vertically overlying a source **102**. For example, the stack **101** may comprise a single deck structure (e.g., the first deck **103**) or a dual deck structure for a 3D memory device (e.g., a 3D NAND Flash memory device) including the first deck **103** and the second deck **105** (FIG. 1D). The first deck **103** (e.g., a lower deck) of the stack **101** may, optionally, be separated from the second deck **105** (e.g., an upper deck) by an interdeck region **134** (FIG. 1D).

(32) The insulative structures **106** may be formed of and include, for example, at least one dielectric material, such as at least one dielectric oxide material (e.g., one or more of SiO.sub.x, phosphosilicate glass, borosilicate glass, borophosphosilicate glass, fluorosilicate glass, AlO.sub.x, HfO.sub.x, NbO.sub.x, TiO.sub.x, ZrO.sub.x, TaO.sub.x, and MgO.sub.x). In some embodiments, the insulative structures **106** are formed of and include SiO.sub.2.

(33) The additional insulative structures **108** may be formed of and include an insulative material that is different than (e.g., has a different chemical composition than), and exhibits an etch selectivity with respect to, the insulative structures **106**. The additional insulative structures **108** may be formed of and include at least one dielectric nitride material (e.g., SiN.sub.y) or at least one oxynitride material (e.g., SiO.sub.xN.sub.y). In some embodiments, the additional insulative structures **108** are formed of and include Si.sub.3N.sub.4.

(34) Prior to forming the stack **101**, the first barrier material **104** may be formed adjacent to (e.g., vertically adjacent to, on) the source **102**. The source **102** and the lowermost one of the insulative structures **106** of the stack **101** are separated from one another by the first barrier material **104**. The first barrier material **104** may be formed of and include at least one insulative material. For example, the first barrier material **104** may comprise a nitride material (e.g., a silicon nitride material, an oxynitride material) located over an upper surface of the source **102**, and may function



as an etch stop material. In some embodiments, the first barrier material **104** comprises a carbon-containing material (e.g., carbon-doped silicon nitride, silicon carbon nitride (SiCN)). As other non-limiting examples, the first barrier material **104** may be formed of and include one or more of silicon, polysilicon, tungsten (W), titanium (Ti), titanium nitride (TiN), aluminum oxide (AlO.sub.x), or another material, so long as the first barrier material **104** is electrically isolated from a lowermost one of the conductive structures of the stack **101**. For example, spacing between the first barrier material **104** and the lowermost one of the conductive structures of the stack **101** may be increased to reduce or eliminate parasitic (e.g., stray) capacitance between adjacent conductive features during use and operation of the electronic device **100**. In some embodiments, the first barrier material **104** comprises amorphous silicon or polycrystalline silicon. In some such embodiments, the first barrier material **104** may be doped with one or more dopants, such as with at least one n-type dopant (e.g., one or more of arsenic, phosphorous, antimony, and bismuth) or at least one p-type dopant (e.g., one or more of boron, aluminum, and gallium). In other embodiments, the first barrier material **104** comprises tungsten. The first barrier material **104** may be substantially homogeneous, or the first barrier material **104** may be heterogeneous.

(35) The first barrier material **104** may include a material composition that is different than a material composition of the insulative structures **106** and the additional insulative structures **108** of the tiers **112**, so that the first barrier material **104** is selectively etchable relative to the insulative structures **106** and the additional insulative structures **108**. A material composition of the first barrier material **104** may also be different than a material composition of subsequently formed materials and structures (e.g., the etch stop material **114**, the additional etch stop material **115**, sacrificial structures **117** (FIG. 1C), and an additional sacrificial structure **119** (FIG. 1C)), so that the first barrier material **104** is selectively etchable relative to each of the subsequently formed materials and structures.

(36) Following formation of the first barrier material **104**, the etch stop material **114** (e.g., a pillar region etch stop material **114**) and the additional etch stop material **115** (e.g., a slot region etch stop material **115**) may be formed within the first barrier material **104**. For example, the etch stop material **114** may be formed to extend within a portion of the first barrier material **104** within the slot region **107**. The additional etch stop material **115** may be formed to extend through the first barrier material **104** to the source **102** within the pillar array regions **109**. In some embodiments, the additional etch stop material **115** extends to an upper surface of the source **102**. In other embodiments, the additional etch stop material **115** extends beyond the upper surface and into at least a portion of the source **102**, as shown in FIG. 1A. Thus, the etch stop material **114** is formed to extend within an upper portion of the first barrier material **104** without extending therethrough (e.g., without extending to the upper surface of the source **102**), and the additional etch stop material **115** directly contacts at least a portion of the source **102**.

(37) As shown in FIG. 1A, a thickness T.sub.1 (e.g., in the Z-direction) of the additional etch stop material **115** may be within a range from about 40 nm to about 200 nm, such as from about 40 nm to about 60 nm, from about 60 nm to about 80 nm, from about 80 nm to 100 nm, from about 100 nm to about 150 nm, or from about 150 nm to about 200 nm. In some embodiments, the thickness T.sub.1 is about 80 nm. However, the disclosure is not so limited and the thickness T.sub.1 may be different than that described above. A thickness T.sub.2 of the first barrier material **104** may be within a range from about 20 nm to about 100 nm, such as from about 20 nm to about 40 nm, from about 40 nm to about 60 nm, from about 60 nm to about 80 nm, or from about 80 nm to about 100 nm. In some embodiments, the thickness T.sub.2 is about 40 nm. However, the disclosure is not so limited and the thickness T.sub.2 may be different than those described. In addition, a thickness T.sub.3 of the etch stop material **114** may be within a range of from about 10 nm to about 60 nm, such as from about 10 nm to about 20 nm, from about 20 nm to about 40 nm, or from about 40 nm to about 60 nm. In some embodiments, the thickness T.sub.3 is about 20 nm. However, the disclosure is not so limited and the thickness T.sub.3 may be different than those described. In

some embodiments, the thickness T.sub.2 is less than the thickness T.sub.1, and the thickness T.sub.3 is less than each of the thickness T.sub.1 and the thickness T.sub.2. In other embodiments, the thickness T.sub.3 of the etch stop material **114** is substantially the same as the thickness T.sub.2 of the first barrier material **104**.

(38) The etch stop material **114** and the additional etch stop material **115** may be selectively etchable relative to one or more of the first barrier material **104**, the insulative structures **106**, the additional insulative structures **108**, as well as subsequently formed materials and structures within the first pillar openings **110** and the first slot **111**. The etch stop material **114** and the additional etch stop material **115** may, for example, comprise one or more of at least one semiconductive material (e.g., a silicon material, such as polysilicon), at least one conductive material, and at least one dielectric material (e.g., one or more of a dielectric oxide, a dielectric nitride, a dielectric oxynitride, and a dielectric carboxynitride). In some embodiments, the etch stop material **114** and the additional etch stop material **115** are formed of and include polysilicon. In additional embodiments, the etch stop material **114** and the additional etch stop material **115** are formed of and include one or more of tungsten and titanium nitride. In further embodiments, the etch stop material **114** and the additional etch stop material **115** are formed of and include aluminum oxide. The etch stop material **114** and the additional etch stop material **115** may or may not include substantially the same material composition as one another.

(39) The etch stop material **114** and the additional etch stop material **115** may be formed using one or more conventional deposition processes, such as one or more of an ALD process, a CVD process, and a PVD process. In some embodiments, portions of one or more of the first barrier material **104** and the source **102** are removed (e.g., through a conventional photolithographic patterning and etching process) to form openings therein; an etch stop material is formed (e.g., deposited) into the openings; and excess portions of the etch stop material are removed (e.g., through a CMP process) to form the etch stop material **114** and the additional etch stop material **115**. Upper surfaces of the etch stop material **114** may be substantially vertically coplanar with upper surfaces of the additional etch stop material **115**. Upper surfaces of the etch stop material **114** and the additional etch stop material **115** may also be substantially vertically coplanar with upper surfaces of the first barrier material **104**. The etch stop material **114** may be at least partially horizontally aligned in a first horizontal direction (e.g., the X-direction) with portions of the additional etch stop material **115**. An elongated portion of the etch stop material **114** underlying the first slot **111** extends in a second horizontal direction (e.g., the Y-direction) substantially orthogonal to each of the first horizontal direction and a vertical direction (e.g., the Z-direction). The etch stop material **114** may be formed to include a substantially continuous material adjacent to (e.g., underlying) the first slot **111** of the slot region **107**. The etch stop material **114** may exhibit a greater lateral extent (e.g., a width in the X-direction) than a lateral extent of the first slot **111**, as shown in FIG. 1A, or, alternatively, sidewalls of the etch stop material **114** may be substantially aligned with sidewalls of the first slot **111**. In other words, portions of the etch stop material **114** may be adjacent to (e.g., underlying) the lowermost one of the insulative structures **106**. The additional etch stop material **115** may include segmented portions thereof adjacent to (e.g., underlying) respective first pillar openings **110** of the pillar array regions **109**. The additional etch stop material **115** may exhibit a greater lateral extent than a lateral extent of the first pillar openings **110** or, alternatively, sidewalls of the additional etch stop material **115** may be substantially aligned with sidewalls of the first pillar openings **110**, as shown in FIG. 1A.

(40) In some embodiments, one or more (e.g., both) of the etch stop material **114** and the additional etch stop material **115** may serve as (e.g., function as) sacrificial structures. For example, in embodiments including the additional etch stop material **115** comprising at least one dielectric material, the additional etch stop material **115** may be removed (e.g., exhumed) prior to formation of pillars (e.g., memory pillars) extending through the stack **101**, such that a channel material of the pillars is electrically connected to the source **102**. In embodiments including the additional etch

stop material **115** comprising a conductive material, for example, the additional etch stop material **115** may remain in the electronic device **100**, without being removed and replaced with subsequently formed materials. In such embodiments, the additional etch stop material **115** may exhibit etch selectivity to surrounding materials without serving as sacrificial structures. In addition, at least portions of the etch stop material **114** may serve as sacrificial structures and additional portions thereof may remain in the electronic device **100**, without being removed and replaced with subsequently formed materials, as described in further detail with reference to FIG. **1F**.

(41) Following formation of the etch stop material **114** and the additional etch stop material **115** within the first barrier material **104**, the stack **101** may be formed on or over the source **102** (e.g., a source tier, a source plate). For example, the first deck **103** of the stack **101** may be formed on or over the source **102** and the first barrier material **104** including the etch stop material **114** and the additional etch stop material **115**. The source **102** may be formed of and include a conductive material such as, for example, a semiconductor material (e.g., polysilicon) doped with at least one p-type dopant (e.g., one or more of boron, aluminum, and gallium) or at least one n-type dopant (e.g., arsenic, phosphorous, antimony). While not illustrated in FIG. **1A**, complementary metal-oxide-semiconductor (CMOS) circuitry may, for example, be present below the source **102**, as described below with reference to FIG. **1N** and FIG. **2**.

(42) The lowermost one of the insulative structures **106** of the stack **101** may be located adjacent the first barrier material **104**. The lowermost one of the insulative structures **106** may be also be located adjacent (e.g., directly on) the etch stop material **114** and the additional etch stop material **115**. As will be described herein, during fabrication of electronic device **100**, one or more portions of the additional insulative structures **108** may be replaced to form conductive structures, such as select gate structures, which may comprise one or more select gate drain (SGD) structures, and an additional select gate structure, which may comprise a select gate source (SGS) structure. In addition, at least some of the insulative structures **106** may be replaced (e.g., substantially entirely replaced) with or, alternatively, supplemented with air gaps.

(43) With continued reference to FIG. **1A** and FIG. **1B**, following formation of the first deck **103** of the stack **101** and prior to formation of the second deck **105** (FIG. **1D**), the first pillar openings **110** may be formed through the stack **101** to, for example, expose the additional etch stop material **115** adjacent to the source **102** within the pillar array regions **109**. The first pillar openings **110** may be formed by conventional techniques. As will be described herein, extended openings of the first pillar openings **110** may be used to form pillars **120** (FIG. **1E**) for forming strings (e.g., strings **170** (FIG. **1K**)) of memory cells (e.g., memory cells **172** (FIG. **1K**)). The first slot **111** may be formed through the stack **101** to, for example, expose the etch stop material **114** within the slot region **107**. The first slot **111** may be formed by conventional techniques. Thus, lower vertical boundaries of the first pillar openings **110** may be defined by the upper surfaces of the additional etch stop material **115** and a lower vertical boundary of the first slot **111** may be defined by the upper surface of the etch stop material **114**. Horizontal boundaries of the first pillar openings **110** and the first slot **111** may be defined by surfaces (e.g., side surfaces) of the first deck **103** of the stack **101** (e.g., surfaces of the insulative structures **106** and the additional insulative structures **108** of the tiers **112**).

(44) The first slot **111** may be formed laterally adjacent to the first pillar openings **110** and exhibit a height substantially similar to (e.g., the same as) a height of the first pillar openings **110**. The first slot **111** may be formed during the same material removal act used to form the first pillar openings **110** or, alternatively, using one or more additional material removal acts. For example, the first slot **111** may be formed during formation of the first pillar openings **110** using a single (e.g., one) masking act to reduce cost and the number of process acts conducted.

(45) Referring to FIG. **1B**, the first pillar openings **110** that laterally neighbor one another in the Y-direction may be offset from each other in the X-direction. Accordingly, the first pillar openings

**110** may be arranged in a so-called “weave pattern,” which may facilitate an increased density of the pillars **120** (FIG. 1E) and the resulting strings (e.g., the strings **170** (FIG. 1K)) of the memory cells (e.g., the memory cells **172** (FIG. 1K)) to be formed in the first pillar openings **110**. However, the disclosure is not so limited and the first pillar openings **110** may be arranged in other patterns (e.g., lines wherein the first pillar openings **110** of each line are aligned with the first pillar openings **110** of each of the other lines). In some embodiments, each first pillar opening **110** may be surrounded by six (6) other first pillar openings **110** and may be arranged in a hexagonal pattern.

(46) The first pillar openings **110** may have any suitable transverse cross-sectional shape such as, for example, a substantially circular cross-sectional shape or a substantially rectangular cross-sectional shape (e.g., a substantially square cross-sectional shape). The first pillar openings **110** may have a horizontal dimension (e.g., diameter)  $D_{sub.1}$  within a range from about 60 nm to about 120 nm, such as from about 60 nm to about 80 nm, from about 80 nm to about 100 nm, or from about 100 nm to about 120 nm. In some embodiments, the horizontal dimension  $D_{sub.1}$  is about 100 nm. However, the disclosure is not so limited and the horizontal dimension  $D_{sub.1}$  may be different than those described. A horizontal dimension (e.g., a width  $W_{sub.1}$  in the X-direction) of the first slot **111**, as well as extended slots formed thereafter, may be within a range of from about 90 nm to about 300 nm, such as from about 90 nm to about 120 nm, from about 120 nm to about 150 nm, from about 150 nm to about 200 nm, or from about 200 nm to about 300 nm. In some embodiments, the width  $W_{sub.1}$  is about 150 nm. However, the disclosure is not so limited and the width  $W_{sub.1}$  may be different than those described. Accordingly, the width  $W_{sub.1}$  of the first slot **111** of the electronic device **100** may be relatively less than that of conventional slots of conventional electronic devices. The reduced width  $W_{sub.1}$  of the first slot **111** relative to that of conventional slots may provide a greater cross-sectional area for formation of the conductive structures of a conductive stack, which in turn may provide a reduced resistivity (e.g., electrical resistance levels) of the conductive materials thereof without significantly affecting conductivity.

(47) Referring to FIG. 1C, the sacrificial structures **117** may be formed in the first pillar openings **110** within the pillar array regions **109** and the additional sacrificial structure **119** may be formed in the first slot **111** within the slot region **107**. The sacrificial structures **117** and the additional sacrificial structure **119** may be configured and positioned to protect the materials (e.g., the insulative structures **106**, the additional insulative structures **108**) of the first deck **103** during additional processing acts to form the second deck **105** over the stack **101**.

(48) The material of the sacrificial structures **117** and the additional sacrificial structure **119** may be selectively etchable relative to one or more of the first barrier material **104**, the insulative structures **106**, the additional insulative structures **108**, the etch stop material **114**, and the additional etch stop material **115**. The sacrificial structures **117** and the additional sacrificial structure **119** may, for example, comprise one or more of at least one semiconductive material (e.g., a silicon material, such as polysilicon), at least one conductive material, and at least one dielectric material (e.g., one or more of a dielectric oxide, a dielectric nitride, a dielectric oxynitride, and a dielectric carboxynitride). In some embodiments, the sacrificial structures **117** and the additional sacrificial structure **119** are formed of and include polysilicon. In additional embodiments, the sacrificial structures **117** and the additional sacrificial structure **119** are formed of and include one or more of tungsten and titanium nitride. In further embodiments, the sacrificial structures **117** and the additional sacrificial structure **119** are formed of and include aluminum oxide. The sacrificial structures **117** and the additional sacrificial structure **119** may or may not include substantially the same material composition as one another.

(49) After forming the sacrificial structures **117** and the additional sacrificial structure **119**, the electronic device **100** may be exposed to a chemical mechanical planarization (CMP) process to remove additional material outside of the first pillar openings **110** and the first slot **111** and to isolate individual portions thereof.

(50) Referring to FIG. 1D, following formation of the sacrificial structures **117** and the additional

sacrificial structure **119** within the first deck **103** of the stack **101**, and prior to formation of the second deck **105**, an insulative material of the interdeck region **134** and plugs **136** may, optionally, be formed to separate the first deck **103** from the second deck **105**. The electronic device **100** may also be formed to include an optional sacrificial material **113** overlying the second deck **105** and an upper insulative material **116** overlying the sacrificial material **113**, if present.

(51) In some embodiments, the second deck **105** may be separated from the first deck **103** by the insulative material of the interdeck region **134**, which may also be referred to herein as an inter-deck oxide. The insulative material of the interdeck region **134** may comprise an oxide material such as, for example, silicon dioxide, aluminum oxide, or another material. In some embodiments, the insulative material of the interdeck region **134** has a different material composition than the material composition of the insulative structures **106** and the additional insulative structures **108**. In other embodiments, the insulative material of the interdeck region **134** has substantially the same material composition as the insulative structures **106**. If present, the interdeck region **134** may have a vertical thickness  $T_{sub.5}$  that is relatively greater than respective vertical thicknesses  $T_{sub.4}$  of the insulative structures **106** of the stack **101**.

(52) The plugs **136** may be formed at upper vertical boundaries (e.g., in the Z-direction) of the sacrificial structures **117** within the pillar array regions **109** to substantially fill (e.g., plug, cover) an upper portion of the sacrificial structures **117**, as shown for simplicity in the right-hand pillar array region **109** in the view of FIG. 1D. If present, the plugs **136** may be formed to extend vertically (e.g., in the Z-direction) into the insulative material of the interdeck region **134** and may cover the sacrificial structures **117** within the first pillar openings **110** (FIG. 1C). The plugs **136** may be configured and positioned to protect the sacrificial structures **117** during additional processing acts to form the second deck **105** over the stack **101**. Each of the plugs **136** may be at least partially (e.g., substantially) horizontally aligned (e.g., in the X-direction and in the Y-direction) with the sacrificial structures **117** vertically thereunder. In some embodiments, the plugs **136** may also be formed to cover the additional sacrificial structure **119** within the slot region **107**. The plugs **136** may be confined within vertical boundaries of the interdeck region **134**. For example, the plugs **136** may not extend into portions of the first deck **103** of the stack **101** underlying the interdeck region **134**. Horizontal boundaries of the plugs **136** may be defined by side surfaces of the insulative material of the interdeck region **134**.

(53) The plugs **136** may individually be formed to exhibit a desired size and shape to cover (e.g., plug, enclose) the sacrificial structures **117**. In some embodiments, each of the plugs **136** is individually formed to exhibit a transverse cross-sectional shape (e.g., a substantially circular cross-sectional shape or a substantially rectangular cross-sectional shape (e.g., a substantially square cross-sectional shape)), and is sized and positioned to cover the sacrificial structures **117**. For example, the plugs **136** may exhibit a substantially circular cross-sectional shape having a substantially circular cross-sectional area sized and positioned to completely cover a cross-sectional area of the sacrificial structures **117**. As shown in FIG. 1D, the plugs **136** may extend beyond horizontal boundaries of the sacrificial structures **117**. In other embodiments, the plugs **136** may exhibit one or more of a different size and shape so long as the plugs **136** cover the sacrificial structures **117**. In embodiments including the plugs **136** formed over the additional sacrificial structure **119**, the plugs **136** may be elongated in a direction of the first slot **111** (e.g., the Y-direction) (See FIG. 1).

(54) The plugs **136** may be formed of and include at least one material formulated to protect one or more of the sacrificial structures **117** and the additional sacrificial structure **119** during additional processing acts to form the second deck **105** over the first deck **103** of the stack **101**. The material of the plugs **136** may be selectively etchable relative to one or more of the insulative material of the interdeck region **134**, the insulative structures **106**, the additional insulative structures **108**, and the upper insulative material **116**. The plugs **136** may, for example, comprise one or more of at least one semiconductive material (e.g., a silicon material, such as polysilicon), at least one conductive

material, and at least one dielectric material (e.g., one or more of a dielectric oxide, a dielectric nitride, a dielectric oxynitride, and a dielectric carboxynitride). In some embodiments, the plugs **136** are formed of and include polysilicon. In additional embodiments, the plugs **136** are formed of and include tungsten. In further embodiments, the plugs **136** are formed of and include titanium nitride.

(55) In other embodiments, the electronic device **100** may not include the interdeck region **134** and the plugs **136** between the first deck **103** and the second deck **105**. In some such embodiments, a lowermost one of the additional insulative structures **108** of the second deck **105** may be formed adjacent to (e.g., directly on) an uppermost one of the insulative structures **106** of the first deck **103**, such that the stack **101** of the electronic device **100** is formed without formation of the interdeck region **134** and the plugs **136**, as shown for simplicity in the left-hand pillar array region **109** in the view of FIG. **1D**. In other words, the lowermost one of the additional insulative structures **108** of the second deck **105** may be formed directly on the uppermost one of the insulative structures **106** of the first deck **103** without intervening materials. While FIGS. **1D** and **1E** show the plug **136** in the right-hand pillar array region **109** and no plug **136** in the left-hand pillar array region **109**, the electronic device **100** would include multiple plugs **136** or no plugs **136** rather than a combination of plugs **136** and no plugs **136**.

(56) The second deck **105** may be formed on or over the first deck **103** of the stack **101**, as well as the interdeck region **134** and the plugs **136**, if present. The second deck **105** may include a vertically alternating sequence of the insulative structures **106** and the additional insulative structures **108** arranged in the tiers **112**, and the upper insulative material **116** may be formed on or over the second deck **105**. The tiers **112** may be formed by conventional techniques. A number (e.g., quantity) of the tiers **112** of the second deck **105** may be equal to (e.g., the same as) a number of the tiers **112** of the first deck **103**, or a quantity of the tiers **112** of the second deck **105** may be different than (e.g., less than, greater than) a quantity of the tiers **112** of the first deck **103**. In other embodiments, the stack **101** includes a single deck (e.g., the first deck **103**) extending between the source **102** and the upper insulative material **116**. In some such embodiments, the single deck may be formed without forming the insulative material of the interdeck region **134** and the plugs **136**. While FIGS. **1D-1N** illustrate the interdeck region **134**, the interdeck region **134** may not be present in some embodiments.

(57) Following formation of the second deck **105**, the sacrificial material **113** may, optionally, be formed over an uppermost one of the insulative structures **106** of the second deck **105**. The sacrificial material **113** may be selectively etchable relative to one or more of the insulative structures **106**, the additional insulative structures **108**, and the upper insulative material **116**. If present, the sacrificial material **113** may include a material composition similar to a material composition of the sacrificial structures **117** and the additional sacrificial structure **119** (e.g., polysilicon, tungsten, titanium nitride, or aluminum oxide).

(58) Formation of the sacrificial material **113** may facilitate formation of one or more staircase structures (e.g., a staircase structure **220** (FIG. **2**)) within a staircase region (e.g., a staircase region **221** (FIG. **2**)) horizontally adjacent to the pillar array regions **109**. The staircase structures **220** are not shown in the perspectives of FIGS. **1A-1P**. The staircase structures **220** may be formed to include steps comprising edges (e.g., horizontal ends) of the tiers **112** of the insulative structures **106** and the additional insulative structures **108**. For example, the staircase structures may be formed in the stack **101** within horizontal boundaries of the staircase region of the electronic device **100** using conventional processes (e.g., conventional photolithographic patterning processes, conventional material removal processes), and conventional processing equipment, which are not described in detail herein. Following formation of the steps of the staircase structures, a dielectric fill material may be formed thereover, and excess portions of the dielectric fill material may be removed (e.g., through a CMP process). The sacrificial material **113**, if present, may be configured and positioned to protect the materials of the second deck **105** within the slot region **107** and the

pillar array regions **109** during processing acts to form the staircase structures. Upon formation of the staircase structures, the sacrificial material **113** may be removed prior to forming the upper insulative material **116**.

(59) The upper insulative material **116**, which may serve as a mask material, may overlie an uppermost one of the tiers **112** of the stack **101**. The upper insulative material **116** may exhibit an etch selectivity relative to one or more of the insulative structures **106** and the additional insulative structures **108**. The upper insulative material **116** may include, by way of non-limiting example, one or more of polysilicon, a dielectric material, a nitride material (e.g., silicon nitride), a metal oxide (e.g., aluminum oxide, titanium oxide, tantalum oxide, tungsten oxide). In some embodiments, the upper insulative material **116** comprises polysilicon. In other embodiments, the upper insulative material **116** includes substantially the same material composition as a material composition of the insulative structures **106** (e.g., SiO<sub>2</sub>).

(60) With continued reference to FIG. **1D**, second pillar openings **110'** (e.g., upper portions of the first pillar openings **110**) may be formed to extend vertically through the upper insulative material **116** and the second deck **105** of the stack **101** to expose upper surfaces of the plugs **136** or, alternatively, to expose upper surfaces of the sacrificial structures **117**. The second pillar openings **110'** may be formed within the pillar array regions **109** without exposing the additional sacrificial structure **119** within the slot region **107**.

(61) During formation of the second pillar openings **110'**, additional openings **140'** (e.g., additional support pillar openings (FIG. **1J**)) may be formed within the electronic device **100**. Formation of the additional openings **140'** may facilitate subsequent formation of additional support pillars (e.g., additional support pillars **164'** (FIG. **1O**)) within one or more of the pillar array regions **109** and the staircase region **221** (FIG. **2**), as described in further detail below. By forming the additional openings **140'** during formation of the second pillar openings **110'**, manufacturing costs may be reduced.

(62) Referring to FIGS. **1E** and **1F**, the sacrificial structures **117** (FIG. **1D**) and underlying portions of the additional etch stop material **115** (FIG. **1D**) may be removed (e.g., exhumed) to expose the source **102** and to form extended openings. One or more materials may be formed within the extended openings to form the pillars **120** including the one or more materials. FIG. **1E** is a simplified cross-sectional view of the electronic device **100** taken along the E-E line of FIG. **1F**, which is a simplified top-down view of the electronic device **100**. With reference to FIGS. **1E** and **1F**, the pillars **120** may extend vertically (e.g., in the Z-direction) through the stack **101**, including the first deck **103** and the second deck **105**.

(63) Portions of the plug material of the plugs **136**, if present, may be selectively removed (e.g., exhumed) to expose respective portions of the sacrificial structures **117** (FIG. **1D**). In embodiments including the interdeck region **134** and the plugs **136**, the interdeck region **134** and portions of the plugs **136** may remain in the electronic device **100**. For convenience, remaining portions of the plugs **136** are not shown in subsequent drawings, although it is understood that the remaining portions of the plugs **136** may be present in the electronic device **100**, in some embodiments.

(64) The materials of the sacrificial structures **117** and, optionally, the additional etch stop material **115** may be substantially removed (e.g., exhumed) to form extended pillar openings **110''** extending vertically through each of the first deck **103** and the second deck **105** of the stack **101**. In some embodiments, the materials of each of the sacrificial structures **117** and the additional etch stop material **115** are removed (e.g., substantially entirely removed) such that the electronic device **100** is substantially devoid (e.g., substantially absent) of the sacrificial structures **117** and the additional etch stop material **115**. In additional embodiments, portions of one or more of the sacrificial structures **117** and the additional etch stop material **115** are selectively removed (e.g., etched) without entirely removing the materials thereof. In embodiments including the additional etch stop material **115** comprising a conductive material, at least a portion of the additional etch stop material **115** may remain in the electronic device **100**. At the processing stage depicted in FIGS. **1E** and **1F**,

the etch stop material **114** and the additional sacrificial structure **119** may still be present within the slot region **107**.

(65) In some embodiments, the extended pillar openings **110"** may extend to the upper surface of the source **102**. Horizontal boundaries of the extended pillar openings **110"** may be defined by surfaces (e.g., side surfaces) of the first deck **103** and the second deck **105** of the stack **101** (e.g., surfaces of the insulative structures **106** and the additional insulative structures **108** of the tiers **112**), the upper insulative material **116**, and remaining portions of the plug material of the plugs **136**, if present. A lower vertical boundary of the extended pillar openings **110"** may be defined by the upper surface of the source **102**. In other embodiments, the extended pillar openings **110"** may extend into a portion of the source **102**, as shown in FIG. **1E**. Accordingly, the horizontal boundaries of the extended pillar openings **110"** may also be defined by surfaces (e.g., side surfaces) of the source **102**. The extended pillar openings **110"** may be configured (e.g., sized and shaped) to receive subsequently formed structures (e.g., the materials of the pillars **120**).

(66) With continued reference to FIGS. **1E** and **1F**, the pillars **120** may extend vertically (e.g., in the Z-direction) through the stack **101**. As will be described herein, the materials of the pillars **120** may be employed to form memory cells (e.g., strings of NAND memory cells). The pillars **120** may each individually comprise a dielectric blocking material **122** horizontally neighboring the levels of the insulative structures **106** and the additional insulative structures **108** of one of the tiers **112** of the stack **101**; a charge blocking material **124** (also referred to as a "dielectric blocking material") horizontally neighboring the dielectric blocking material **122**; a memory material **126** horizontally neighboring the charge blocking material **124**; a tunnel dielectric material **128** (also referred to as a "tunneling dielectric material") horizontally neighboring the memory material **126**; a channel material **130** horizontally neighboring the tunnel dielectric material **128**; and an insulative material **132** in a center portion of the pillars **120**. The channel material **130** may be horizontally interposed between the insulative material **132** and the tunnel dielectric material **128**; the tunnel dielectric material **128** may be horizontally interposed between the channel material **130** and the memory material **126**; the memory material **126** may be horizontally interposed between the tunnel dielectric material **128** and the charge blocking material **124**; the charge blocking material **124** may be horizontally interposed between the memory material **126** and the dielectric blocking material **122**; and the dielectric blocking material **122** may be horizontally interposed between the charge blocking material **124** and the levels of the insulative structures **106** and additional insulative structures **108**.

(67) The dielectric blocking material **122** may be formed of and include one or more of a metal oxide (e.g., one or more of aluminum oxide, hafnium oxide, zirconium oxide, lanthanum oxide, yttrium oxide, tantalum oxide, gadolinium oxide, niobium oxide, titanium oxide), a dielectric silicide (e.g., aluminum silicide, hafnium silicate, zirconium silicate, lanthanum silicide, yttrium silicide, tantalum silicide), and a dielectric nitride (e.g., aluminum nitride, hafnium nitride, lanthanum nitride, yttrium nitride, tantalum nitride). In some embodiments, the dielectric blocking material **122** comprises aluminum oxide. In other embodiments, the pillars **120** do not include the dielectric blocking material **122**, and the charge blocking material **124** horizontally neighbors the levels of the insulative structures **106** and additional insulative structures **108**.

(68) The charge blocking material **124** may be formed of and include a dielectric material such as, for example, one or more of an oxide (e.g., silicon dioxide), a nitride (silicon nitride), and an oxynitride (silicon oxynitride), or another material. In some embodiments, the charge blocking material **124** comprises silicon oxynitride.

(69) The memory material **126** may comprise a charge trapping material or a conductive material. The memory material **126** may be formed of and include one or more of silicon nitride, silicon oxynitride, polysilicon (doped polysilicon), a conductive material (tungsten, molybdenum, tantalum, titanium, platinum, ruthenium, and alloys thereof, or a metal silicide such as tungsten silicide, molybdenum silicide, tantalum silicide, titanium silicide, nickel silicide, cobalt silicide, or



a combination thereof), a semiconductive material polycrystalline or amorphous semiconductor material including at least one elemental semiconductor element or at least one compound semiconductor material, conductive nanoparticles (e.g., ruthenium nanoparticles), metal dots. In some embodiments, the memory material **126** comprises silicon nitride.

(70) The tunnel dielectric material **128** may be formed of and include a dielectric material through which charge tunneling can be performed under suitable electrical bias conditions, such as through hot-carrier injection or by Fowler-Nordheim tunneling induced charge transfer. By way of non-limiting example, the tunnel dielectric material **128** may be formed of and include one or more of silicon oxide, silicon nitride, silicon oxynitride, dielectric metal oxides (such as aluminum oxide and hafnium oxide), dielectric metal oxynitride, dielectric metal silicates, alloys thereof, and/or combinations thereof. In some embodiments, the tunnel dielectric material **128** comprises silicon dioxide. In other embodiments, the tunnel dielectric material **128** comprises nitrogen, such as an oxynitride. In some such embodiments, the tunnel dielectric material **128** comprises silicon oxynitride.

(71) In some embodiments the tunnel dielectric material **128**, the memory material **126**, and the charge blocking material **124** together may comprise a structure configured to trap a charge, such as, for example, an oxide-nitride-oxide (ONO) structure. In some such embodiments, the tunnel dielectric material **128** comprises silicon dioxide, the memory material **126** comprises silicon nitride, and the charge blocking material **124** comprises silicon dioxide. In other embodiments, the tunnel dielectric material **128**, the memory material **126**, and the charge blocking material **124** together comprise an oxide-nitride-oxynitride structure. In some such embodiments, the tunnel dielectric material **128** comprises silicon oxynitride, the memory material **126** comprises silicon nitride, and the charge blocking material **124** comprises silicon dioxide.

(72) The channel material **130** may be formed of and include one or more of a semiconductor material (at least one elemental semiconductor material, such as polycrystalline silicon; at least one III-V compound semiconductor material, at least one II-VI compound semiconductor material, at least one organic semiconductor material, GaAs, InP, GaP, GaN, other semiconductor materials), and an oxide semiconductor material. In some embodiments, the channel material **130** includes amorphous silicon or polysilicon. In some embodiments, the channel material **130** comprises a doped semiconductor material. The insulative material **132** may be formed of and include at least one insulative material. In some embodiments, the insulative material **132** comprises silicon dioxide.

(73) After forming the pillars **120**, vertically (e.g., in the Z-direction) surfaces of the electronic device **100** may be exposed to a chemical mechanical planarization (CMP) process to remove laterally (e.g., in the X-direction, in the Y-direction) portions of the dielectric blocking material **122**, the charge blocking material **124**, the memory material **126**, the tunnel dielectric material **128**, the channel material **130**, and the insulative material **132**.

(74) Referring to FIG. 1F, the etch stop material **114** (shown in dashed lines) may include sacrificial portions **114a** and remaining portions **114b** proximate to and intervening between neighboring portions of the sacrificial portions **114a**. For example, the sacrificial portions **114a** of the etch stop material **114** may initially be present in one or more areas (shown in dashed lines) designated for the subsequently formed support pillars (e.g., support pillars **164** (FIG. 1O)) within the slot region **107**, and the remaining portions **114b** of the etch stop material **114** may be present in regions between the one or more areas designated for the support pillars. The etch stop material **114** may be formed to horizontally extend in the second horizontal direction (e.g., in the Y-direction) within the slot region **107**, as described with reference to FIG. 1B. Accordingly, elongated portions of the etch stop material **114** may initially be formed to include a substantially continuous material in openings of the first barrier material **104** (FIG. 1E), and the remaining portions **114b** of the etch stop material **114** may remain in the electronic device **100** following formation of the support pillars, as described below with reference to FIG. 1O. Further, one or more additional areas (shown

in dashed lines) within the pillar array regions **109** may also be designated for subsequently formed additional support pillars (e.g., the additional support pillars **164'** (FIG. **1O**)), as shown in the left-hand pillar array region **109** in the view of FIG. **1F**.

(75) Referring now to FIG. **1G**, a second barrier material **118** may be formed adjacent to (e.g., on or over) the upper insulative material **116** and the pillars **120**. In some embodiments, the second barrier material **118** may include a material composition similar to a material composition of the first barrier material **104** including, for example, a nitride material, a carbon-containing material (e.g., carbon-doped silicon nitride, silicon carbon nitride), or one or more of polysilicon, tungsten, titanium, titanium nitride, and aluminum oxide. Accordingly, the second barrier material **118** may include a material composition that is different than a material composition of the insulative structures **106**, the additional insulative structures **108**, the etch stop material **114**, and the upper insulative material **116**, so that the second barrier material **118** is selectively etchable relative to such materials and structures.

(76) A conductive contact structure **135** (e.g., a conductive plug) may be formed in electrical communication with the channel material **130** of the pillars **120**. For example, in some embodiments, a portion of the insulative material **132** within the pillars **120** may be selectively removed to form a recessed portion in each of the pillars **120**. After selectively removing the insulative material **132**, the conductive contact structure **135** may be formed within the recess of each pillar **120** and in electrical communication with the channel material **130**. The conductive contact structure **135** may be formed of and include a conductive material (e.g., polysilicon). The conductive contact structure **135** may comprise sharp corners or, alternatively, the conductive contact structure **135** may comprise rounded corners, as shown in FIG. **1G**.

(77) In other embodiments, the insulative material **132** of each pillar **120** may not be recessed. In some such embodiments, openings may be formed in the second barrier material **118** at locations corresponding to the locations of the pillars **120** to expose upper (e.g., in the Z-direction) portions of the channel material **130**. The conductive contact structures **135** may be formed in the openings and in electrical communication with the channel material **130**. In some embodiments, an additional channel material (e.g., such as a channel liner) is formed within the openings of the second barrier material **118** and in electrical communication with the channel material **130**, and the conductive contact structures **135** are formed in remaining portions of the openings and in electrical communication with the additional channel material.

(78) The conductive contact structure **135** may be in electrical communication with, for example, a conductive line for providing access to strings (e.g., the strings **170** (FIG. **1K**)) of the memory cells (e.g., the memory cells **172** (FIG. **1K**)) formed from the pillars **120**.

(79) Additional portions of the second barrier material **118** may be formed on or over upper surfaces of the conductive contact structures **135** and initial portions of the second barrier material **118**, as shown in dashed lines for clarity. For ease of understanding the disclosure, the initial portions and the additional portions of the second barrier material **118** are hereinafter collectively referred to as the second barrier material **118**, as shown in FIG. **1G**. The second barrier material **118** may be homogeneous (e.g., may include a single material), or may be heterogeneous (e.g., may include a stack including at least two different materials). The additional portions of the second barrier material **118** may be configured and positioned to protect the pillars **120** including the conductive contact structures **135** during additional processing acts.

(80) As shown in FIG. **1G**, a second slot **111'** (e.g., an upper portion of the first slot **111**) may be formed to extend vertically through the second barrier material **118**, the upper insulative material **116**, and the second deck **105** of the stack **101** to expose the upper surface of the additional sacrificial structure **119** within the slot region **107**.

(81) Referring to FIG. **1H**, a material of the additional sacrificial structure **119** (FIG. **1G**) may be substantially removed (e.g., exhumed) to form an extended slot **111''** extending vertically through the second barrier material **118**, the upper insulative material **116**, as well as the first deck **103** and

the second deck **105** of the stack **101**. In some embodiments, the material of the additional sacrificial structure **119** is removed (e.g., substantially entirely removed) such that the electronic device **100** is substantially devoid (e.g., substantially absent) of the additional sacrificial structure **119**. In additional embodiments, portions of the additional sacrificial structure **119** are selectively removed (e.g., etched) without entirely removing the material thereof.

(82) In some embodiments, the extended slot **111"** may extend to an upper surface of the etch stop material **114**. Horizontal boundaries of the extended slot **111"** may be defined by surfaces (e.g., side surfaces) of the first deck **103** and the second deck **105** of the stack **101** (e.g., surfaces of the insulative structures **106** and the additional insulative structures **108** of the tiers **112**), the upper insulative material **116**, and the second barrier material **118**. A lower vertical boundary of the extended slot **111"** may be defined by the upper surface of the etch stop material **114**. The extended slot **111"** may be configured (e.g., sized and shaped) to receive subsequently formed structures (e.g., the support pillars **164** (FIG. 1N)) within designated portions thereof.

(83) The extended slot **111"** may divide the stack **101** into multiple blocks **137**. The blocks **137** may each extend in substantially the same horizontal direction (e.g., the Y-direction) as one another, and neighboring blocks **137** may be horizontally separated (e.g., in the X-direction) from one another by the extended slot **111"** within the slot region **107**. Each of the blocks **137** may exhibit substantially the same geometric configuration (e.g., dimensions, shape) as each other of the blocks **137** in the pillar array regions **109**. In addition, horizontally neighboring blocks **137** may all be horizontally separated from one another by substantially the same distance (e.g., corresponding to the width  $W_{sub.1}$  of the first slot **111** (FIG. 1B) and the extended slot **111"**). Accordingly, the blocks **137** may be substantially uniformly (e.g., non-variably, equally, consistently) sized, shaped, and spaced relative to one another.

(84) With continued reference to FIG. 1H, a third barrier material **138** may be formed in the extended slot **111"** to extend vertically (e.g., in the Z-direction) through the stack **101**. The third barrier material **138** may be formed to extend substantially entirely through the first deck **103** and the second deck **105** of the stack **101** within the slot region **107**, substantially filling the extended slot **111"**. In some embodiments, the third barrier material **138** may include a material composition similar to a material composition of one or more of the first barrier material **104** and the second barrier material **118** including, for example, a nitride material, a carbon-containing material (e.g., carbon-doped silicon nitride, silicon carbon nitride), or one or more of polysilicon, tungsten, titanium, titanium nitride, and aluminum oxide. Accordingly, the third barrier material **138** may include a material composition that is different than a material composition of the insulative structures **106**, the additional insulative structures **108**, the etch stop material **114**, and the upper insulative material **116**, so that the third barrier material **138** is selectively etchable relative to such materials and structures. In other embodiments, a material composition of the third barrier material **138** may differ from a material composition of one or more (e.g., each) of the first barrier material **104** and the second barrier material **118**, so long as the third barrier material **138** is selectively etchable relative to the surrounding materials and structures.

(85) As will be described herein, portions of the third barrier material **138** remain in the electronic device **100** following formation of conductive structures of a conductive stack, without being removed and replaced with subsequently formed materials. In other words, portions of the third barrier material **138** may remain within the extended slot **111"** of the slot region **107** without serving as sacrificial structures. For example, the third barrier material **138** may include sacrificial portions overlying the sacrificial portions **114a** (FIG. 1F) of the etch stop material **114** and remaining portions overlying the remaining portions **114b** (FIG. 1F) of the etch stop material **114** proximate to and intervening between neighboring portions of the sacrificial portions of the third barrier material **138**. Similar to the sacrificial portions **114a** of the etch stop material **114**, the sacrificial portions of the third barrier material **138** may initially be formed in one or more areas designated for the subsequently formed support pillars (e.g., support pillars **164** (FIG. 1O)) within

the slot region **107**, and the remaining portions of the third barrier material **138** may be formed in regions between the one or more areas designated for the support pillars.

(86) By providing the portions of the third barrier material **138** that remain within the slot region **107** during formation of the conductive structures, such configurations may, for example, reduce or substantially prevent undesirable tier deformations (e.g., tier warping) and/or tier collapse during the formation of the conductive structures. For example, the third barrier material **138** may be formed within the extended slot **111"** of the slot region **107** of the stack **101** prior to conducting replacement gate processing acts, and portions of the third barrier material **138** may remain within the slot region **107** during such processing acts to provide further structural support to the stack **101** during the formation of the conductive structures. Such a configuration may substantially prevent the risk of undesirable current leakage and short circuits during use and operation of the electronic device **100** without significantly affecting conductivity.

(87) Referring to FIGS. **11** and **1J**, after forming the third barrier material **138** within the slot region **107**, portions thereof may be selectively removed (e.g., etched) to expose respective portions of the etch stop material **114** and to form openings **140** (e.g., support pillar openings). FIG. **1I** is a simplified cross-sectional view of the electronic device **100** taken along the I-I line of FIG. **1J**, which is a simplified top-down view of the electronic device **100**. With reference to FIGS. **1I** and **1J**, the openings **140** may extend vertically through the stack **101**, including the first deck **103** and the second deck **105**.

(88) The openings **140** may extend to the upper surface of the etch stop material **114**. Horizontal boundaries of the openings **140** may be defined by surfaces (e.g., side surfaces) of the first deck **103** and the second deck **105** of the stack **101** (e.g., surfaces of the insulative structures **106** and the additional insulative structures **108** of the tiers **112**), the upper insulative material **116**, the second barrier material **118**, and the remaining portions of third barrier material **138**. A lower vertical boundary of the openings **140** may be defined by the upper surface of the etch stop material **114**. The openings **140** may be configured (e.g., sized and shaped) to receive subsequently formed structures (e.g., the support pillars **164** (FIG. **1N**)).

(89) At the processing stage depicted in FIGS. **1I** and **1J**, the sacrificial portions **114a** of the etch stop material **114** may still be present within the slot region **107**, such that the etch stop material **114** includes the substantially continuous material along a length of the extended slot **111"** (FIG. **1H**) within the slot region **107**. In other words, the sacrificial portions **114a** of the etch stop material **114** define lower boundaries of the openings **140** and the remaining portions **114b** thereof are located under remaining portions of the third barrier material **138**, as shown in FIG. **1J**.

(90) Referring to FIG. **1J**, the openings **140** within the slot region **107** may horizontally (e.g., in the X-direction) neighbor the pillars **120** (shown in dashed lines) within the pillar array regions **109**. For example, the openings **140** may be horizontally aligned in columns extending in the Y-direction within the slot region **107** (e.g., between neighboring blocks **137**). In some embodiments, a single line of the openings **140** extends in the Y-direction within the extended slot **111"** (FIG. **1H**). In other words, the openings **140** are separated from one another in the Y-direction by the third barrier material **138**, such that individual openings **140** do not overlap one another, and only one (e.g., a single) of the openings **140** horizontally separates the neighboring blocks **137** in the X-direction.

(91) The openings **140** may have any suitable transverse cross-sectional shape such as, for example, a substantially circular cross-sectional shape or a substantially rectangular cross-sectional shape (e.g., a substantially square cross-sectional shape). The cross-sectional shape of support pillars **164** (see FIG. **1N**) subsequently formed in the openings **140** may be tailored to provide sufficient mechanical support to the electronic device **100** without substantial conductivity loss of the electronic device **100**. In some embodiments, each of the openings **140** may individually exhibit a substantially circular cross-sectional shape having a substantially circular cross-sectional area. In other embodiments, at least some of the openings **140** may individually exhibit an elongate cross-sectional shape, such as an oblong cross-sectional shape. While three openings **140** are

shown in FIG. 1J for clarity, any number of the openings **140** may be formed within the slot region **107** and laterally adjacent to the pillars **120** within the pillar array regions **109** of the electronic device **100**.

(92) The openings **140** may have a horizontal dimension (e.g., diameter)  $D_{sub.2}$  within a range from about 100 nm to about 400 nm, such as from about 100 nm to about 150 nm, from about 150 nm to about 200 nm, from about 200 nm to about 250 nm, from about 250 nm to about 300 nm, from about 300 nm to about 350 nm, or from about 350 nm to about 400 nm. In some embodiments, the horizontal dimension  $D_{sub.2}$  is about 275 nm. However, the disclosure is not so limited and the horizontal dimension  $D_{sub.2}$  may be different than those described. In some embodiments, the horizontal dimension  $D_{sub.2}$  may be relatively larger than the horizontal dimension  $D_{sub.1}$ . In other embodiments, the horizontal dimension  $D_{sub.2}$  may be substantially the same as or, alternatively, less than the horizontal dimension  $D_{sub.1}$ . In some embodiments, a horizontal dimension (e.g., a width  $W_{sub.2}$  in the X-direction) of the etch stop material **114** may correspond to (e.g., may be substantially the same as) the horizontal dimension  $D_{sub.2}$  of the openings **140**. The width  $W_{sub.2}$  in a first horizontal direction (e.g., the X-direction) may be relatively larger than the width  $W_{sub.1}$  of the first slot **111** (FIG. 1B) and, thus, the extended slot **111'** (FIG. 1H) in the first horizontal direction. Accordingly, the horizontal dimension  $D_{sub.2}$  in the first horizontal direction may be relatively larger than the width  $W_{sub.1}$  in the first horizontal direction, substantially orthogonal to a second horizontal direction (e.g., the Y-direction) in which the extended slot **111'** extends. In other embodiments, the width  $W_{sub.2}$  and, thus, the horizontal dimension  $D_{sub.2}$  may be substantially the same as or, alternatively, less than the width  $W_{sub.1}$ .

(93) In some embodiments, the openings **140** may initially be formed to have a smaller horizontal dimension, and thereafter (e.g., at the processing stage of FIG. 1L) the openings **140** may be enlarged to exhibit the horizontal dimension  $D_{sub.2}$ . In embodiments including the horizontal dimension  $D_{sub.2}$  of the openings **140** being relatively larger than or substantially the same as the width  $W_{sub.1}$ , the remaining portions **114b** of the etch stop material **114** may be spaced apart from one another in at least one horizontal direction (e.g., the Y-direction). In other words, the remaining portions **114b** of the etch stop material **114** may include discrete (e.g., discontinuous) portions in at least one horizontal direction. As used herein, the term “discrete” means and includes a material or structure that is defined by one or more differing materials or structures. For example, the openings **140** may segment individual remaining portions **114b** of the etch stop material **114** from one another.

(94) In embodiments including the horizontal dimension  $D_{sub.2}$  of the openings **140** being less than the width  $W_{sub.1}$ , the remaining portions **114b** of the etch stop material **114** may include a substantially continuous material, and the etch stop material **114** may substantially laterally surround (e.g., substantially continuously laterally surround) lower regions of the openings **140**, as well as the support pillars formed therein. Further, the third barrier material **138** may include a substantially continuous material within the slot region **107**, and the third barrier material **138** may substantially laterally surround (e.g., substantially continuously laterally surround) regions of the openings **140** at an elevational level above the etch stop material **114**, as well as the support pillars subsequently formed therein.

(95) A horizontal dimension  $D_{sub.3}$  (e.g., a distance in the Y-direction) between neighboring openings **140** (e.g., between an outer perimeter thereof) may be within a range from about 100 nm to about 2000 nm (e.g., 2  $\mu\text{m}$ ), such as from about 100 nm to about 500 nm, from about 500 nm to about 1000 nm, from about 1000 nm to about 1500 nm, or from about 1500 nm to about 2000 nm. In some embodiments, the horizontal dimension  $D_{sub.3}$  is about 1500 nm (e.g., 1.5  $\mu\text{m}$ ). However, the disclosure is not so limited and the horizontal dimension  $D_{sub.3}$  may be different than those described. For example, the horizontal dimension  $D_{sub.3}$  may be less than those described (e.g., less than 100 nm, less than 50 nm), so long as the openings **140** are separated by portions of the third barrier material **138** that are thick enough to withstand subsequent processing of the electronic

device **100**. In some embodiments, the horizontal dimension D.sub.3 may be less than or equal to a horizontal dimension (e.g., a distance in the X-direction) of a respective block **137**. Further, the horizontal dimension D.sub.3 may be about three times (3×) greater than the horizontal dimension D.sub.2 of the openings **140**. In other words a ratio of the D.sub.3:D.sub.2 (e.g., a ratio of the distance between neighboring openings **140** to the diameter of the openings **140**) is about 3:1. In some embodiments, the D.sub.3:D.sub.2 ratio is substantially even (e.g., 1:1). In other embodiments, the D.sub.3:D.sub.2 ratio is less than 1:1 (e.g., 1:2, 1:3, or 1:4). However, the disclosure is not so limited and the D.sub.3:D.sub.2 ratio may be different than those described. The D.sub.3:D.sub.2 ratio may be tailored to have a desired value between neighboring openings **140** to the diameter of the openings **140** that may be selected at least partially based on design requirements of the electronic device **100**.

(96) As shown in FIG. 1J, the additional openings **140'** may be formed within the stack **101** prior to or, alternatively, during formation of the openings **140**. The additional openings **140'** may be formed around a perimeter (e.g., near lateral edges) of the pillar array regions **109**, without being formed within the slot region **107**. For example, the additional openings **140'** may be formed within or proximate to the staircase structures (e.g., the staircase structure **220** (FIG. 2)) within the staircase region (e.g., the staircase region **221** (FIG. 2)) horizontally adjacent to the pillar array regions **109**. Additionally, or alternatively, at least some of the additional openings **140'** may be formed within central regions of individual blocks **137** of the stack **101** within one or more of the pillar array regions **109**. For example, the additional openings **140'** may be formed in one or more rows along a midline centrally located between neighboring slot regions **107**, without being formed within the slot region **107**. The additional openings **140'** may be configured (e.g., sized and shaped) to be substantially the same as the openings **140** and may be formed during formation thereof. For example, a horizontal dimension (e.g., diameter) of the additional openings **140'** may or may not be substantially the same as the horizontal dimension D.sub.2 of the openings **140**. By forming the additional openings **140'** during formation of the openings **140**, manufacturing costs may be reduced.

(97) The additional openings **140'** located external to the slot region **107** may be used to form additional support pillars (e.g., the additional support pillars **164'** (FIG. 1O)). At least some of the additional support pillars may, for example, be configured to extend vertically (e.g., in the Z-direction) through the stack **101** and physically contact (e.g., land on) a structure within the source **102** to facilitate a predetermined function (e.g., an electrical interconnection function) in addition to providing a support function.

(98) Additionally, or alternatively, the additional support pillars formed within the additional openings **140'** may be configured as support structures without providing electrical interconnection (e.g., to the source **102** (FIG. 1I)) and serve primarily (e.g., only) to provide mechanical support within one or more of the pillar array regions **109** and the staircase region **221** (FIG. 2). In some embodiments, at least some of the additional openings **140'** are formed prior to formation of the openings **140** (e.g., during formation of the second pillar openings **110'** (FIG. 1D), during formation of the extended slot **111''** (FIG. 1H)). In some such embodiments, at least some of the additional openings **140'** may be filled with the third barrier material **138** during formation of the third barrier material **138** within the extended slot **111''** at the processing stage depicted in FIG. 1H. For example, the third barrier material **138** formed in the additional openings **140'** may remain in the electronic device **100**, without being removed and replaced with subsequently formed materials. In other words, the third barrier material **138** may remain in at least some of the additional openings **140'** without serving as sacrificial structures. By forming the third barrier material **138** of the additional support pillars within the additional openings **140'** during formation of the third barrier material **138** within the slot region **107**, manufacturing costs may be reduced. Forming the third barrier material **138** in the additional openings **140'** prior to formation of the conductive structures may provide enhanced structural support during formation of the conductive structures,

which may further reduce or substantially prevent undesirable tier deformations and/or tier collapse during the formation of the conductive structures.

(99) Referring to FIG. 1K, the sacrificial portions **114a** (FIG. 1J) of the etch stop material **114** (FIG. 1J) may be selectively removed (e.g., exhumed) to expose the first barrier material **104**, without exposing the source **102**. In other embodiments, the source **102** may be exposed through the openings **140**. The openings **140** (also referred to herein as “replacement gate openings”) may facilitate replacement of the additional insulative structures **108** (FIG. 1I) to form conductive structures **144** through so-called “replacement gate” or “gate last” processing acts. Accordingly, the processing acts to replace the additional insulative structures **108** with the conductive structures **144** may be performed through segmented portions of the openings **140** (e.g., support pillar openings) rather than through conventional replacement gate slots (e.g., corresponding to the extended slot **111**” (FIG. 1H)) as in conventional replacement gate processes. As described above, by providing the portions of the third barrier material **138** that remain within the slot region **107** during formation of the conductive structures **144**, such configurations may, for example, reduce or substantially prevent undesirable tier deformations and/or tier collapse during the formation of the conductive structures **144**.

(100) The additional insulative structures **108** (FIG. 1I) may be selectively removed (e.g., exhumed) through the openings **140**. In some embodiments, the additional insulative structures **108** are removed by exposing the additional insulative structures **108** to a so-called “wet nitride strip” comprising a wet etchant comprising phosphoric acid. Resulting spaces formed between vertically neighboring (e.g., in the Z-direction) insulative structures **106** may be filled with one or more conductive materials to form the conductive structures **144** and a stack **141** including tiers **142** of the insulative structures **106** and the conductive structures **144**. The conductive structures **144** may be located at locations corresponding to the previous locations of the additional insulative structures **108** removed through the openings **140**. In some embodiments, residual portions of the additional insulative structures **108** may be removed by subsequently exposing the insulative material thereof to additional wet etch and/or dry etch chemistries, for example, in one or more additional material removal processes prior to forming the conductive structures **144**.

(101) The conductive structures **144** may be formed of and include any conductive material including, but not limited to, n-doped polysilicon, p-doped polysilicon, undoped polysilicon, or a metal. In some embodiments, the conductive structures **144** comprise n-doped polysilicon. In other embodiments, the conductive structures **144** comprise tungsten. The conductive material of each of the conductive structures **144** may individually include a substantially homogeneous composition, or a substantially heterogeneous composition. In some embodiments, the conductive material of each of the conductive structures **144** of each of the tiers **142** of the stack **141** exhibits a substantially homogeneous composition. In additional embodiments, at least one of the conductive structures **144** of at least one of the tiers **142** of the stack **141** exhibits a substantially heterogeneous composition. The conductive structures **144** of each of the tiers **142** of the stack **141** may each be substantially planar, and may each exhibit a desired thickness.

(102) Formation of the conductive structures **144** may form the strings **170** of the memory cells **172**, each memory cell **172** located at an intersection of a conductive structure **144** and the memory cell materials (e.g., the dielectric blocking material **122**, the charge blocking material **124**, the memory material **126**, and the tunnel dielectric material **128**) and the channel material **130**.

(103) Although the electronic device **100** has been described and illustrated as comprising the memory cells **172** having a particular configuration, the disclosure is not so limited. In some embodiments, the memory cells **172** may comprise so-called “MONOS” (metal-oxide-nitride-oxide-semiconductor) memory cells. In additional embodiments, the memory cells **172** comprise so-called “TANOS” (tantalum nitride-aluminum oxide-nitride-oxide-semiconductor) memory cells, or so-called “BETANOS” (band/barrier engineered TANOS) memory cells, each of which are subsets of MONOS memory cells. In other embodiments, the memory cells **172** comprise so-called

“floating gate” memory cells including floating gates (e.g., metallic floating gates) as charge storage structures. The floating gates may horizontally intervene between central structures of the strings **170** and the conductive structures **144**.

(104) At least one lower conductive structure **144** of the stack **141** may be employed as at least one lower select gate (e.g., at least one source side select gate (SGS)) of the electronic device **100**. In some embodiments, a single (e.g., only one) conductive structure **144** of a vertically lowermost tier **142** of the stack **141** is employed as a lower select gate (e.g., a SGS) of the electronic device **100**. In addition, upper conductive structure(s) **144** of the stack **141** may be employed as upper select gate(s) (e.g., drain side select gate(s) (SGDs)) of the electronic device **100**. In some embodiments, horizontally-neighboring conductive structures **144** of a vertically uppermost tier **142** of the stack **141** (e.g., separated from each other by additional slot structures) are employed as upper select gates (e.g., SGDs) of the electronic device **100**. In some embodiments, more than one (e.g., two, four, five, six) conductive structures **144** are employed as an upper select gate (e.g., a SGD) of the electronic device **100**.

(105) Formation of the conductive structures **144** may form conductive levels **145** vertically neighboring insulative levels **147** of the insulative structures **106** and vertically interposed between (vertically interleaved with) vertically neighboring insulative structures **106**. In some embodiments, the conductive levels **145** are located within vertical boundaries defined by vertically neighboring insulative structures **106**, and the insulative levels **147** are located within vertical boundaries defined by vertically neighboring conductive structures **144**.

(106) The remaining insulative structures **106** may extend laterally in a cantilever fashion and exhibit a relatively large aspect ratio (e.g., a ratio of a length of the insulative structures **106** (e.g., in the X-direction) to a thickness (e.g., in the Z-direction) thereof). A length of the insulative structures **106** between the pillars **120** and the openings **140** may be within a range from, for example, about 300 nm to about 350 nm, such as from about 300 nm to about 325 nm or from about 325 nm to about 350 nm. Of course, the disclosure is not so limited and the length may be different than those described. In some embodiments, the length is larger at lower portions of the stack **101** relative to other portions. Due to the large length relative to the thickness of insulative structures, the insulative structures of conventional electronic devices may be prone to failure and collapse. In addition, due to the larger length at the lower portions of the stack **101** (e.g., lower portions of the first deck **103**) relative to other portions, the lowermost insulative structures **106** may be more prone to collapsing. However, since the third barrier material **138** extends substantially entirely through the stack **101** within the slot region **107** and is formed at an extreme edge of the insulative structures **106** immediately proximate the openings **140**, the lowermost insulative structures **106** may be less prone to collapse compared to the insulative structures of conventional electronic devices.

(107) Referring to FIG. **1L**, after forming the conductive structures **144** of the conductive levels **145**, portions thereof may, optionally, be removed through the openings **140** to form recessed regions **146**. For example, the conductive structures **144** may be exposed to one or more etch chemistries to selectively remove a conductive material of the conductive structures **144** and any surrounding materials (e.g., a conductive liner material) through the openings **140**. The one or more etch chemistries may include one or more wet etchants, one or more dry etchants, or both. In some embodiments, the conductive structures **144** are exposed to a wet etchant. Accordingly, exposed surfaces (e.g., side surfaces) of the conductive structures **144** may be horizontally recessed relative to exposed surfaces (e.g., side surfaces) of the insulative structures **106** of the insulative levels **147** proximate the openings **140**.

(108) Formation of the recessed regions **146** may facilitate formation of additional conductive structures (e.g., additional conductive material, conductive rails) formed horizontally adjacent (e.g., horizontally on) at least some of the conductive structures **144** of the conductive levels **145**. Since the openings **140** occupy regions proximate to horizontal ends of the conductive structures **144**, the



electrical resistance exhibited by the conductive structures **144** of the tiers **142** of FIG. **1L** may be greater than desired. To lower the electrical resistance, the additional conductive structures may be formed to extend (e.g., laterally extend) from the exposed surfaces of the conductive structures **144** within the openings **140**. In other embodiments, the recessed regions **146** may be filled with one or more insulative materials.

(109) In additional embodiments, the conductive structures **144** may not be recessed relative to the exposed surfaces of the insulative structures **106**, such that the recessed regions **146** are not formed in the electronic device **100**. Rather, residual portions of the conductive material of the conductive structures **144** within the openings **140** may be removed (e.g., etched) to isolate the conductive structures **144** (e.g., access lines, word lines) without recessing the conductive structures **144** relative to the insulative structures **106**. Further, in embodiments including the openings **140** being initially formed to have a smaller horizontal dimension at the processing stage of FIGS. **1I** and **1J**, the openings **140** may be enlarged at the processing stage of FIG. **1L**, for example, to exhibit the horizontal dimension  $D_{sub.2}$  (See FIG. **1J**). In some such embodiments, exposed surfaces of each of the first barrier material **104**, the insulative structures **106**, the conductive structures **144**, the upper insulative material **116**, and the second barrier material **118** are recessed (e.g., substantially equally recessed) to enlarge the openings **140**.

(110) Referring to FIG. **1M**, following formation of the conductive structures **144** through the openings **140**, one or more of the insulative structures **106** (FIG. **1L**) and the upper insulative material **116** (FIG. **1L**) may, optionally, be selectively removed (e.g., exhumed) through the openings **140**. The insulative structures **106** and the upper insulative material **116** may be removed by exposing the respective materials to wet etch and/or dry etch chemistries, for example, in one or more material removal processes. Accordingly, lateral openings **148** may be formed between vertically neighboring (e.g., in the Z-direction) conductive structures **144** within the stack **141**, and an additional lateral opening **150** may be formed between an uppermost one of the conductive structures **144** and the second barrier material **118**. The lateral openings **148** may be located at locations corresponding to the previous locations of the insulative structures **106** removed through the openings **140**, and the additional lateral opening **150** may be located at a location corresponding to the location of the upper insulative material **116** removed through the openings **140**. In some embodiments, entire portions of at least some (e.g., each) of the insulative structures **106** and the upper insulative material **116** may be removed (e.g., substantially entirely removed). In some such embodiments, residual portions of the insulative structures **106** and/or the upper insulative material **116** may be removed through the openings **140** by subsequently exposing the insulative materials thereof to additional wet etch and/or dry etch chemistries, for example, in one or more additional material removal processes. In other embodiments, at least portions of the insulative structures **106** and/or the upper insulative material **116** may remain in the lateral openings **148** and the additional lateral opening **150**, respectively. Additional process acts (e.g., material removal process acts) may be performed to electrically isolate the memory cells **172**.

(111) As shown in FIG. **1M**, after forming the lateral openings **148** and the additional lateral opening **150**, a liner material **152** may be formed within the openings **140**. In some embodiments, the liner material **152** is formed adjacent to (e.g., directly laterally adjacent to) side surfaces of the second barrier material **118** and the conductive structures **144** exposed within the openings **140**. After forming the liner material **152**, the electronic device **100** may be exposed to a chemical mechanical planarization (CMP) process to remove additional material outside of the openings **140** and to isolate individual portions thereof.

(112) The liner material **152** may be formed of and include at least one dielectric material having a lower dielectric constant ( $K$ ) than a silicon nitride ( $Si_{sub.3}N_{sub.4}$ ) material. By way of non-limiting example, the liner material **152** may comprise one or more of silicon oxycarbide ( $SiO_{sub.x}C_{sub.y}$ ), silicon oxynitride ( $SiO_{sub.x}N_{sub.y}$ ), hydrogenated silicon oxycarbide ( $SiC_{sub.x}O_{sub.y}H_{sub.z}$ ), and silicon oxycarbonitride ( $SiO_{sub.x}C_{sub.y}N_{sub.z}$ ). In some

embodiments, the liner material **152** comprises SiO.sub.xC.sub.yN.sub.z. In additional embodiments, a different dielectric material (e.g., an oxide material, such as a dielectric oxide material, having a dielectric constant lower than the dielectric constant of a silicon oxide (SiO.sub.x, SiO.sub.2) material or of a carbon-doped silicon oxide material that includes silicon atoms, carbon atoms, oxygen atoms, and hydrogen atoms) may be employed as the liner material **152**. In some embodiments, the liner material **152** may function as an insulator having a dielectric constant (K) within a range of from about 1.9 to about 3.2, such as within a range of from about 1.9 to about 2.7, from about 2.7 to about 3.0, or from about 3.0 to about 3.2. In some embodiments, the dielectric constant (K) of the liner material **152** is about 3.0.

(113) For example, the liner material **152** may be formed of and include a so-called “low-K dielectric material.” As used herein, the term “low-K dielectric material” means and includes a dielectric material, such as a dielectric nitride material or a dielectric oxide material, having a dielectric constant (K) lower than the dielectric constant of a silicon nitride (Si.sub.3N.sub.4) material, of a silicon oxide (SiO.sub.x, SiO.sub.2) material, or of a carbon-doped silicon oxide material that includes silicon atoms, carbon atoms, oxygen atoms, and hydrogen atoms. The dielectric constant of silicon dioxide is from about 3.7 to about 3.9 and the dielectric constant of silicon nitride is about 7.5. The term “low-K dielectric material” is a relative term and is distinguished from the term “dielectric material” by a relative value of its dielectric constant. In some embodiments, the liner material **152** is formed of and includes a low-K dielectric material. In other embodiments, the liner material **152** comprises silicon dioxide. Further, a material composition of the liner material **152** may be the same as, or different than, a material composition of the insulative structures **106** (FIG. 1L).

(114) With continued reference to FIG. 1M, one or more air gaps **154** (e.g., voids, unfilled volumes) may be formed in the lateral openings **148** in place of one or more of the insulative structures **106** (FIG. 1L) of the insulative levels **147**. Further, an additional air gap **156** may be formed in the additional lateral opening **150** in place of the upper insulative material **116** (FIG. 1L). Accordingly, at least some of the air gaps **154** and the additional air gap **156** may be laterally interposed between portions of the liner material **152** and the pillars **120** (e.g., the dielectric blocking material **122** thereof). The pillars **120** within individual blocks **137** may be horizontally separated from one another by the air gaps **154** and the additional air gap **156**. The air gaps **154** may be in direct vertical alignment with the conductive structures **144** and located within horizontal boundaries thereof. In some embodiments, lateral side boundaries of the air gaps **154** are substantially vertically aligned with lateral side surfaces of at least some of the conductive structures **144**. Upper boundaries of the additional air gap **156** may be vertically aligned with or, alternatively, vertically below upper surfaces of one or more of the pillars **120** and the conductive contact structures **135**.

(115) The insulative structures **106** and the upper insulative material **116** may be replaced (e.g., substantially replaced) with or, alternatively, supplemented with the air gaps **154** and the additional air gap **156**, respectively. For example, the insulative levels **147** may be substantially devoid (e.g., substantially absent) of an insulative material (e.g., an oxide material) within horizontal boundaries of the conductive structures **144**. In some embodiments, at least some of the air gaps **154** and the additional air gap **156** include a gaseous material (e.g., air, oxygen, nitrogen, argon, helium, or a combination thereof). In other embodiments, the air gaps **154** and the additional air gap **156** include a vacuum (e.g., a space entirely void of matter).

(116) The liner material **152** may be formed within the lateral openings **148** and the additional lateral opening **150** to effectively “pinch off” and close (e.g., seal) the lateral openings **148** and the additional lateral opening **150** immediately adjacent to the openings **140** resulting in formation of the air gaps **154** and the additional air gap **156**. The liner material **152** may be formed to vertically extend between neighboring conductive structures **144** within the lateral openings **148** of the insulative levels **147**, such that the liner material **152** substantially completely vertically fills

outermost portions of the lateral openings **148** proximate the openings **140** without entirely filling the lateral openings **148**. Similarly, the liner material **152** may be formed to vertically extend between the uppermost one of the conductive structures **144** and the second barrier material **118** within the additional lateral opening **150**, such that the liner material **152** substantially completely vertically fills an outermost portion of the additional lateral opening **150** proximate the openings **140** without entirely filling the additional lateral opening **150**.

(117) Formation of the liner material **152** may result in formation of so-called “bread loafing” regions of the liner material **152** within the lateral openings **148** and the additional lateral opening **150**. Accordingly, formation of the liner material **152** through the openings **140** may usefully result in the bread loafing regions being present between the openings **140** and the horizontally neighboring pillars **120**. In other words, process acts may be selected to provide (e.g., facilitate, promote) the bread loafing regions of the liner material **152** proximate the openings **140** for formation of the air gaps **154** and the additional air gap **156** between the openings **140** and the horizontally neighboring pillars **120**. In some embodiments, additional materials (e.g., additional portions of the liner material **152**) may be formed within the outermost portions of the lateral openings **148** and the additional lateral opening **150** to effectively “pinch off” and close the lateral openings **148** and the additional lateral opening **150** at lateral edges of the stack **141** to form the air gaps **154** and the additional air gap **156**. Formation of the additional materials may or may not result in bread loafing regions thereof being present between the lateral edges of the stack **141** and the pillars **120**.

(118) The air gaps **154** and the additional air gap **156** may be located distal from the openings **140** and proximate (e.g., directly laterally adjacent) to the pillars **120**. The pillars **120** may be substantially surrounded by the additional air gap **156** at an elevational level of the conductive contact structures **135**. The air gaps **154** may be located within the insulative levels **147** and may be defined by the liner material **152**, the pillars **120**, and the conductive structures **144**. The additional air gap **156** may be defined by the liner material **152**, the pillars **120**, the uppermost one of the conductive structures **144**, and the second barrier material **118**. A lateral side boundary of the air gaps **154** may be substantially vertically aligned with a lateral side surface of at least some of the conductive structures **144** proximate the pillars **120**. Elongated portions of the air gaps **154** may extend in at least one horizontal direction (e.g., the X-direction, the Y-direction) with at least a portion of the air gaps **154** being located directly adjacent to the dielectric blocking material **122** of the pillars **120**. In some embodiments, the air gaps **154** exhibit a substantially rectangular profile in at least one horizontal direction (e.g., the X-direction) and extending substantially parallel to a major surface of the source **102**. In some embodiments, the air gaps **154** include laterally extending volumes between the vertically neighboring conductive structures **144**, such that a single (e.g., one) air gap **154** is within a single, undivided space at each of the tiers **142** of the stack **141**.

(119) As shown in FIG. 1M, the air gaps **154** may be formed to have a desired height  $H_{\text{sub.1}}$ , and the additional air gap **156** may be formed to have a height  $H_{\text{sub.2}}$  that is relatively greater than the height  $H_{\text{sub.1}}$  of the air gaps **154**. By way of non-limiting example, the height  $H_{\text{sub.1}}$  of the air gaps **154**, may be within a range of from about 10 nm to about 40 nm, such as from about 10 nm to about 20 nm, from about 20 nm to about 30 nm, or from about 30 nm to about 40 nm. The height  $H_{\text{sub.2}}$  of the additional air gap **156**, may be within a range of from about 20 nm to about 60 nm, such as from about 20 nm to about 30 nm, from about 30 nm to about 40 nm, from about 40 nm to about 50 nm, or from about 50 nm to about 60 nm. The height  $H_{\text{sub.2}}$  of the additional air gap **156** may be relatively larger than the height of one of the conductive structures **144** and relative larger than a combined height of the air gaps **154** and one of the conductive structures **144** of one of the tiers **142**. In addition, the liner material **152** may be formed to any desired thickness, such as a thickness less than or equal to about 60 nm, such as within a range of from about 20 nm to about 30 nm, from about 30 nm to about 40 nm, from about 40 nm to about 50 nm, or from about 50 nm to about 60 nm. In some embodiments, one or more additional materials (e.g., a cap material, a nitride

material) may be formed adjacent to the liner material **152** within or proximate the additional lateral opening **150** to facilitate uniform coverage of the relatively larger height H.sub.2 of the additional air gap **156** within the additional lateral opening **150**. Forming the electronic device **100** to include the liner material **152**, the air gaps **154**, and the additional air gap **156** may facilitate improved performance of the electronic device **100**.

(120) In some embodiments, the air gaps **154** and the additional air gap **156** may function as an insulator having a dielectric constant (K) of about 1. Further, the air gaps **154** and the additional air gap **156** may improve performance of the electronic device **100** by providing improved insulative properties laterally adjacent to the pillars **120**, through decreased dielectric constant relative to the insulative structures **106** (FIG. 1L) and the upper insulative material **116** (FIG. 1L). The air gaps **154** may limit capacitance (e.g., parasitic capacitance, stray capacitance) between the vertically neighboring conductive structures **144**, and may reduce cross-talk therebetween. The additional air gap **156** may further limit capacitance between the uppermost one of the conductive structures **144** and the conductive contact structures **135** of the pillars **120**, and may reduce cross-talk therebetween. For example, the additional air gap **156** may be configured (e.g., sized, shaped) to reduce parasitic (e.g., stray) capacitance between lateral portions of the uppermost one of the conductive structures **144** proximate the pillars **120** and the conductive contact structures **135**.

(121) For example, the liner material **152**, the air gaps **154**, and the additional air gap **156**, according to embodiments of the disclosure may reduce bridging and/or parasitic capacitance between the conductive structures **144** and between the conductive contact structures **135** and the uppermost one of the conductive structures **144** relative to configurations wherein the liner material **152** and the air gaps **154** are not present. The reduced capacitance may, in turn, provide a reduced programming time, in some instances. The liner material **152** laterally adjacent to the pillars **120** may allow for reduced parasitic capacitance between neighboring conductive structures **144**, without the need to increase a thickness of such insulating structures of the insulative levels **147**. Presence of the additional air gap **156** proximate to the pillars **120** and laterally adjacent to the liner material **152** also allows for reduced parasitic capacitance between the conductive contact structures **135** and the uppermost one of the conductive structures **144**. By lowering parasitic capacitance between adjacent structures using the air gaps **154** and the additional air gap **156**, bridging and/or parasitic capacitance of the associated structures may be further reduced within the electronic device **100**. As a result, the RC (product of resistance and capacitance) of the conductive structures may be optimized, which may correlate to an increase in the performance of an apparatus containing the electronic device **100** by allowing for a reduction in operational speed (e.g., programming time). Furthermore, the methods of the disclosure may reduce or eliminate process acts utilized to form many conventional electronic devices that may be used for similar operations as the electronic device **100**. Accordingly, the electronic device **100** according to embodiments of the disclosure may be formed utilizing fewer process acts than conventional electronic devices.

(122) In contrast, conventional configurations including an insulative material (e.g., an oxide material) laterally adjacent to pillar structures corresponding to the pillars **120** may have a dielectric constant of about 3.7 or greater. Accordingly, a portion of an uppermost conductive structure (e.g., corresponding to the uppermost conductive structure) of a conventional configuration may be susceptible to electrical contact (e.g., bridging) with conductive contact structures (e.g., corresponding to the conductive contact structures **135**) and/or with conductive lines during subsequent process acts, as well as during use and operation of the conventional electronic devices including such conventional configuration.

(123) Referring to FIGS. 1N and 1O, after forming the air gaps **154** and the additional air gap **156** using the liner material **152**, additional conductive structures may be formed adjacent to (e.g., on or over) the pillars **120**, and the support pillars **164** may be formed within the openings **140** (FIG. 1M). FIG. 1N is a simplified cross-sectional view of the electronic device **100** taken along the N-N line of FIG. 1O, which is a simplified top-down view of the electronic device **100**. FIG. 1P

illustrates an enlarged portion of box **172** of FIG. **1N** and illustrates a memory cell **172**, in accordance with embodiments of the disclosure. With reference to FIGS. **1N** and **1O**, in some embodiments, a so-called “punch through” etch may be performed to remove portions of the liner material **152** and to expose the underlying portions of the first barrier material **104**, and portions of the first barrier material **104** thereunder may be selectively removed (e.g., exhumed) to expose the underlying source **102**. In other embodiments, portions of the liner material **152** and the first barrier material **104** may remain between the source **102** and the support pillars **164**, such as when electrical interconnection is not provided therebetween. In addition, remaining portions of one or more of the additional etch stop material **115** (FIG. **1D**) and the first barrier material **104** underlying the pillars **120**, if present, may be removed to expose the source **102**, and electrical interconnection may be provided between the channel material **130** of the pillars **120** and the source **102**.

(124) Portions of the second barrier material **118** (e.g., the additional portions thereof) overlying the conductive contact structures **135** may be selectively removed to form contact openings **158** therein and to expose the conductive contact structures **135**. Conductive contacts **160** (e.g., contacts, pillar contacts) may be formed in the contact openings **158** extending vertically through the second barrier material **118**. For example, a conductive material may be formed (e.g., deposited) into the contact openings **158**, and excess portions of the conductive material may be removed (e.g., through a CMP process) to form the conductive contacts **160**. The conductive contacts **160** may be formed of and include at least one conductive material. In some embodiments, the conductive contacts **160** are formed of and include one or more of tungsten, titanium, and titanium nitride.

(125) The conductive contacts **160** may be adjacent to (e.g., vertically adjacent to, on) and in direct electrical contact with the conductive contact structures **135**. In some embodiments, the conductive contacts **160** may be formed to horizontally extend over an entire exposed surface of the conductive contact structures **135**, as shown in FIG. **1N**. In other embodiments, the conductive contacts **160** may be formed to horizontally extend over only a portion of the exposed surface of the conductive contact structures **135**. Following formation of the conductive contacts **160**, interconnect structures (e.g., filled contact vias, filled bit line vias) may, optionally, be formed adjacent to (e.g., on or over) the upper surfaces of the conductive contacts **160**, and conductive lines (e.g., data lines **202** (FIG. **2**)) may be formed thereover. For simplicity, the interconnect structures are not shown in FIG. **1N**.

(126) With continued reference to FIGS. **1N** and **1O**, a fill material **162** of the support pillars **164** may be formed adjacent (e.g., over) the liner material **152**, substantially filling the openings **140** (FIG. **1M**). In some embodiments, the fill material **162** is formed of and includes an insulative material, such as a silicon oxide material. In other embodiments, the fill material **162** is formed of and includes at least one conductive material including, but not limited to, n-doped polysilicon, p-doped polysilicon, undoped polysilicon, or at least one other conductive material, such as one or more of tungsten, titanium, and titanium nitride. The liner material **152** may substantially surround sidewalls of the fill material **162**.

(127) The fill material **162** of the support pillars **164** may be formed to substantially fill remaining portions of the openings **140** (FIG. **1M**) extending vertically through the first deck **103** and the second deck **105** of the stack **141** and to the source **102**. The support pillars **164** may be within or proximate to the slot region **107** between the blocks **137** and may be confined within the slot region **107** of the electronic device **100**. At least some of the support pillars **164** (e.g., including the insulative material) may be formed to extend vertically from an upper surface of the second barrier material **118** overlying the second deck **105** to an upper surface of the source **102**. Alternatively or additionally, at least some of the support pillars **164** (e.g., including the conductive material as the fill material **162**) may be formed to extend below the upper surface of the source **102** and into portions thereof (shown in dashed lines). For example, some of the support pillars **164** may be

configured to extend vertically (e.g., in the Z-direction) through the stack **141** and physically contact (e.g., land on) a structure within the source **102** to facilitate a predetermined function (e.g., an electrical interconnection function, a support function) of the support pillars **164**. Accordingly, at least portions of the support pillars **164** (e.g., the fill material **162**) may extend to a lower depth than a depth to which the third barrier material **138** extends. In some embodiments, each of the support pillars **164** functions as active support pillars and is configured to provide electrical interconnection within the electronic device **100**. In other embodiments, at least some of the support pillars **164** do not provide electrical interconnection and serve primarily (e.g., only) to provide mechanical support. The number of active support pillars and mechanical support (e.g., dummy) pillars may be determined, at least in part, on the number of support pillars **164** provided, as well as the spacing (e.g., the horizontal dimension  $D_{sub.3}$  (FIG. 1J)) therebetween.

(128) In some embodiments, such as when the fill material **162** of the support pillars **164** includes a conductive material, the fill material **162** may be formed during formation of the conductive contacts **160**. By forming the fill material **162** of the support pillars **164** during formation of the conductive contacts **160**, manufacturing costs may be reduced. After forming the fill material **162**, the electronic device **100** may be exposed to a chemical mechanical planarization (CMP) process to remove additional material outside of the openings **140** (FIG. 1M) and to isolate individual portions thereof. Upper surfaces of each of the support pillars **164**, the conductive contacts **160**, and the second barrier material **118** may be substantially coplanar with one another.

(129) The second barrier material **118** may substantially surround sidewalls of the liner material **152** of the support pillars **164** at an elevational level of one or more of the conductive contacts **160** and the conductive contact structures **135**, as shown in FIG. 1O. Further, portions of the third barrier material **138** that remain within the slot region **107** may at least partially laterally surround the support pillars **164** and be in direct contact with the sidewalls of the liner material **152** of the support pillars **164**. In some embodiments, the third barrier material **138** may substantially continuously laterally surround at least some (e.g., each) of the support pillars **164**. Accordingly, the support pillars **164** are laterally separated from one another by the third barrier material **138** along a vertical height of the support pillars **164**. In some embodiments, a single line of the support pillars **164** extends in the Y-direction within the extended slot **111'** (FIG. 1H), such that only one (e.g., a single) of the support pillars **164** horizontally separates the neighboring blocks **137** in the X-direction. Further, the support pillars **164** are separated from one another in the Y-direction by the third barrier material **138**, such that individual support pillars **164** do not overlap one another. Accordingly, each of the support pillars **164** is discrete (e.g., discontinuous) from each other of the support pillars **164** with portions of the third barrier material **138** extending therebetween. Further, individual portions of the fill material **162** of respective support pillars **164** are separated from one another by the liner material **152** and the third barrier material **138**, such that the fill material **162** is discontinuous along the extended slot **111'**.

(130) As shown in FIGS. 1N and 1O, formation of the support pillars **164** (e.g., the liner material **152** and the fill material **162**) within the slot region **107** may result in formation of slot structures **165**. The slot structures **165** may include the remaining portions **114b** of the etch stop material **114**, the remaining portions of the third barrier material **138**, as well as the liner material **152** and the fill material **162** of the support pillars **164**. In other words, each of the remaining portions **114b** of the etch stop material **114**, the remaining portions of the third barrier material **138**, and the support pillars **164** (e.g., the liner material **152** and the fill material **162**) define the slot structures **165**. Thus, the blocks **137** of the pillar array regions **109** are separated from one another by the slot structures **165** within the slot region **107**, which slot structures **165** include multiple (e.g., two or more) materials and structures including differing material compositions from one another. Accordingly, the materials of the slot structures **165** within the slot region **107** of the electronic device **100** may include additional materials and structures than that of conventional slot structures of conventional electronic devices. The additional materials (e.g., the third barrier material **138**)

and structures (e.g., the support pillars **164**) relative to that of conventional slot structures may, for example, reduce or substantially prevent undesirable tier deformations (e.g., tier warping) and/or tier collapse during the formation of the conductive structures. The additional materials and structures, in turn, may substantially prevent the risk of undesirable current leakage and short circuits during use and operation of the electronic device **100** without significantly affecting conductivity.

(131) The electronic device **100** may further include at least one control unit **174** (e.g., control device) underlying the stack **141**. For example, the control unit **174** may be positioned under the source **102**. The control unit **174** may include devices and circuitry for controlling various operations of other components of the electronic device **100**. By way of non-limiting example, the control unit **174** may include one or more (e.g., each) of charge pumps (e.g., V<sub>sub</sub>.CCP charge pumps, V<sub>sub</sub>.NEGWL charge pumps, DVC2 charge pumps); delay-locked loop (DLL) circuitry (e.g., ring oscillators); drain supply voltage (V<sub>sub</sub>.dd) regulators; devices and circuitry for controlling column operations for arrays (e.g., arrays of vertical memory strings) to subsequently be formed within the electronic device **100**, such as one or more (e.g., each) of decoders (e.g., column decoders), sense amplifiers (e.g., equalization (EQ) amplifiers, isolation (ISO) amplifiers, NMOS sense amplifiers (NSAs), PMOS sense amplifiers (PSAs)), repair circuitry (e.g., column repair circuitry), I/O devices (e.g., local I/O devices), memory test devices, array multiplexers (MUX), and error checking and correction (ECC) devices; and devices and circuitry for controlling row operations for arrays (e.g., arrays of the strings **170**) within memory regions of the electronic device **100**, such as one or more (e.g., each) of decoders (e.g., row decoders), drivers (e.g., word line (WL) drivers), repair circuitry (e.g., row repair circuitry), memory test devices, MUX, ECC devices, and self-refresh/wear leveling devices. In some embodiments, the control unit **174** includes CMOS (complementary metal-oxide-semiconductor) circuitry. In such embodiments, the control unit **174** may be characterized as having a “CMOS under Array” (“CuA”) configuration.

(132) As shown in FIG. 1N, the control unit **174** may include circuitry **178** in electrical communication with one or more of the source **102** and the fill material **162** of the support pillars **164**. Contacts **176** (e.g., conductive contacts) may, optionally, electrically connect the circuitry **178** of the control unit **174** and the fill material **162** of the support pillars **164**. For example, the contacts **176** may extend through a portion of insulative materials of the source **102** and, optionally, through a portion of the first barrier material **104**, if present in the slot region **107**, to provide electrical connection between the support pillars **164** and the circuitry **178**, although other configurations of connections therebetween may be contemplated. For example, the fill material **162** of the support pillars **164** may directly contact a structure within the source **102**.

(133) With reference to FIG. 1O, in some embodiments, the remaining portions **114b** of the etch stop material **114** may be spaced apart from one another in at least one horizontal direction (e.g., the Y-direction). In some such embodiments, the support pillars **164** segment individual remaining portions **114b** of the etch stop material **114** from one another, as described above with reference to FIG. 1J. In other embodiments, the remaining portions **114b** of the etch stop material **114** may include a substantially continuous material, and the etch stop material **114** may substantially laterally surround (e.g., substantially continuously laterally surround) lower portions of the support pillars **164**.

(134) The additional support pillars **164'** may be formed within the additional openings **140'** (FIG. 1J) within the stack **141** prior to or, alternatively, during formation of the support pillars **164**. For example, the fill material **162** of the support pillars **164** and the additional support pillars **164'** may be formed in a single processing act. The additional support pillars **164'** may be formed around a perimeter (e.g., near lateral edges) of the pillar array regions **109**, without being formed within the slot region **107**, as described in further detail above. At least some of the additional support pillars **164'** may, for example, be configured to extend vertically (e.g., in the Z-direction) through the stack **141** and physically contact a structure (e.g., the contacts **176**) within the source **102** to facilitate a

predetermined function (e.g., an electrical interconnection function) in addition to providing a support function. Additionally, or alternatively, the additional support pillars **164'** including the third barrier material **138**, for example, may be configured as support structures without providing electrical interconnection and serve primarily (e.g., only) to provide mechanical support within one or more of the pillar array regions **109** and the staircase region **221** (FIG. 2).

(135) As shown in FIG. 1O, the neighboring blocks **137** may be horizontally separated (e.g., in the X-direction) from one another by the support pillars **164** of the slot structures **165** within the slot region **107**. The horizontal dimension  $D_{sub.2}$  of the support pillars **164** in the first horizontal direction (e.g., the X-direction) may be relatively larger than the width  $W_{sub.1}$  of the extended slot **111'** (FIG. 1H) in the first horizontal direction, substantially orthogonal to the second horizontal direction (e.g., the Y-direction) in which the extended slot **111'** extends. By providing the third barrier material **138** and the support pillars **164** within the slot structures **165**, the support pillars **164** may provide enhanced structural support to the stack **141** to facilitate formation of the air gaps **154** and the additional air gap **156**.

(136) Accordingly, the stack **141** of the electronic device **100** may include the third barrier material **138** of the slot structures **165** within the slot region **107** and horizontally proximate to the pillars **120** within the pillar array regions **109**. In addition, the support pillars **164** of the slot structures **165** may be positioned within the slot region **107** and configured (e.g., sized and shaped) to inhibit (e.g., prevent) undesirable tier deformations (e.g., tier warping) and/or tier collapse. For example, the support pillars **164**, in combination with the third barrier material **138**, of the slot structures **165** within the slot region **107** may provide increased structural support at locations horizontally proximate to the horizontal ends (e.g., horizontal boundaries in the X-direction) of large cantilever structures of the insulative structures **106** (FIG. 1L) of the insulative levels **147** during replacement gate processing acts. In other words, formation of the third barrier material **138** within the slot region **107** facilitates formation of the openings **140** (FIG. 1M) within the slot region **107** prior to performing replacement gate processing acts, such that the additional insulative structures **108** (FIG. 1I) may be replaced with the conductive structures **144** through the openings **140**. The support pillars **164** and the third barrier material **138** may also provide structural support to the conductive structures **144** to facilitate formation of the air gaps **154** and the additional air gap **156**.

(137) The configuration of the support pillars **164** and the third barrier material **138** of the slot structures **165** within the slot region **107** may substantially reduce or substantially prevent the risk of undesirable current leakage and short circuits in the stack **141** during use and operation of the electronic device **100**, compared to conventional electronic devices lacking the support structures, without significantly affecting conductivity of the conductive structures **144**. For example, the material of the third barrier material **138** may be selectively etchable relative to the material of one or more of the insulative structures **106** (FIG. 1L) and the additional insulative structures **108** (FIG. 1I) to minimize (e.g., prevent) loss of material thereof during subsequent process acts.

(138) In contrast, conventional electronic devices may exhibit differential stress (e.g., differing compressive stress) on adjacent structures as a result of local stresses existing in large cantilever structures (e.g., insulative structures of tiers) in the bottom of a conductive stack. In addition, conventional electronic devices may exhibit wafer bow as a result of differing lengths among the insulative structures due to tapering of adjacent structures (e.g., pillars, staircase structures) at differing elevations of the conductive stack. The local stresses on adjacent structures and the wafer bow may result in contact misalignment (e.g., misalignment between conductive contacts and conductive structures of the tiers). By way of contrast, the support pillars **164** and the third barrier material **138** of the slot structures **165** within the slot region **107** according to embodiments of the disclosure may provide additional mechanical support at horizontal ends of the cantilever structures compared to only providing conventional support pillars within the pillar array regions.

(139) In some instances, damage may occur to conventional support pillars during formation of conventional slots. Particularly, damage to the materials of the support pillars, also called



“clipping,” may be a source of defects, which can adversely affect electronic device performance. Accordingly, the support pillars **164** may be formed within the slot region **107** following formation of the extended slot **111** (FIG. **1H**) in order to substantially reduce (e.g., substantially prevent) damage to the support pillars **164** during fabrication. Further, formation of the support pillars **164** within the slot region **107** may provide increased structural support within the stack **141**, without undesirably increasing the overall width (e.g., horizontal footprint) of the stack **141** within the pillar array regions **109**. For example, providing the support pillars **164** (e.g., active support structures, mechanical support structures) within the slot region **107** may reduce a number of support structures (e.g., the additional support pillars **164'**) within the pillar array regions **109** and the staircase region **221** (FIG. **2**), which facilitates a greater cross-sectional area for formation of the conductive structures **144** of the stack **141**.

(140) FIG. **1P** illustrates an enlarged portion of box **172** of FIG. **1N** and illustrates a memory cell **172**, in accordance with embodiments of the disclosure. With reference to FIG. **1P**, the memory cells **172** may each include the channel material **130** horizontally neighboring the insulative material **132**, the tunnel dielectric material **128** horizontally neighboring the channel material **130**, the memory material **126** horizontally neighboring the tunnel dielectric material **128**, the charge blocking material **124** horizontally neighboring the memory material **126**, the dielectric blocking material **122** horizontally neighboring the charge blocking material **124**, and the conductive structures **144** horizontally neighboring the dielectric blocking material **122**.

(141) In some embodiments, and as illustrated in FIG. **1P**, a dielectric barrier material **166** may, optionally, be formed directly neighboring the dielectric blocking material **122** or, alternatively, the charge blocking material **124** and directly neighboring the air gaps **154** of the tiers **142**. A conductive liner material **168** may directly neighbor the dielectric barrier material **166** and the conductive structures **144**, in some embodiments. For example, the dielectric barrier material **166** may initially be formed directly adjacent to the dielectric blocking material **122**, if present, or the charge blocking material **124** and the insulative structures **106** (FIG. **1L**). The conductive liner material **168** may be formed directly adjacent to the dielectric barrier material **166** prior to formation of the air gaps **154** in spaces previously occupied by the insulative structures **106**. In embodiments including the dielectric blocking material **122** of the pillars **120**, the dielectric barrier material **166** may not be present. For ease of illustration and understanding, the dielectric barrier material **166** and the conductive liner material **168** are not illustrated in FIG. **1N**, but it will be understood that the electronic device **100** may include one or both of the dielectric barrier material **166** and the conductive liner material **168**.

(142) The dielectric barrier material **166** may be formed of and include one or more of a metal oxide (e.g., one or more of aluminum oxide, hafnium oxide, zirconium oxide, lanthanum oxide, yttrium oxide, tantalum oxide, gadolinium oxide, niobium oxide, titanium oxide), a dielectric silicide (e.g., aluminum silicide, hafnium silicate, zirconium silicate, lanthanum silicide, yttrium silicide, tantalum silicide), and a dielectric nitride (e.g., aluminum nitride, hafnium nitride, lanthanum nitride, yttrium nitride, tantalum nitride). In some embodiments, the dielectric barrier material **166** comprises aluminum oxide.

(143) The conductive liner material **168** may be formed of and include a seed material from which the conductive structures **144** may be formed. The conductive liner material **168** may be formed of and include, for example, a metal (e.g., titanium, tantalum), a metal nitride (e.g., tungsten nitride, titanium nitride, tantalum nitride), or another material. In some embodiments, the conductive liner material **168** comprises titanium nitride. In other embodiments, the dielectric barrier material **166** is in direct contact with each of the conductive structures **144** and the electronic device **100** is substantially (e.g., entirely) devoid of the conductive liner material **168** between the dielectric barrier material **166** and the conductive structures **144**. In other words, each of the tiers **142** lack a titanium nitride material between the air gap **154** and the conductive structures **144**, in some embodiments.

(144) Accordingly, in some embodiments, an electronic device comprises a stack comprising tiers of alternating conductive levels and insulative levels overlying a source, slots extending vertically through the stack and dividing the stack into blocks, and support pillars within the slots and extending vertically through the stack. The support pillars exhibit a lateral dimension in a first horizontal direction relatively larger than a lateral dimension of the slots in the first horizontal direction, substantially orthogonal to a second horizontal direction in which the slots extend.

(145) Accordingly, in at least some embodiments, a method of forming an electronic device comprises forming pillars in a stack comprising alternating first materials and second materials within an array region. The stack overlies a source. The method comprises forming slots extending vertically through the stack and dividing the stack into blocks, forming a barrier material within the slots, and forming support pillar openings through the barrier material. The method comprises replacing the first materials of the stack with one or more conductive materials through the support pillar openings, and forming support pillars within the support pillar openings and extending vertically through the stack. The support pillars exhibit a lateral dimension in a first horizontal direction relatively larger than a lateral dimension of the slots in the first horizontal direction, substantially orthogonal to a second horizontal direction in which the slots extend.

(146) FIG. 2 illustrates a partial cutaway perspective view of a portion of an electronic device **200** (e.g., a microelectronic device, a memory device, such as a 3D NAND Flash memory device) including one or more electronic device structures **201** (e.g., a microelectronic device structure). The electronic device **200** may be substantially similar to the electronic device **100** previously described with reference to FIGS. 1A through 1P. As shown in FIG. 2, the electronic device structure **201** of the electronic device **200** may include the staircase structure **220** within the staircase region **221** defining contact regions for connecting interconnect lines **206** to conductive structures **205** (e.g., corresponding to the conductive structures **144** (FIG. 1N)). The electronic device structure **201** may include vertical strings **207** (e.g., corresponding to the strings **170** (FIG. 1N)) of memory cells **203** (e.g., corresponding to the memory cells **172** (FIG. 1N)) that are coupled to each other in series. The vertical strings **207** may extend vertically (e.g., in the Z-direction) and orthogonally to conductive lines and the conductive structures **205**, such as the data lines **202**, a source tier **204** (e.g., corresponding to the source **102** (FIG. 1N)), the interconnect lines **206**, first select gates **208** (e.g., upper select gates, drain select gates (SGDs)), select lines **209**, and a second select gate **210** (e.g., a lower select gate, a source select gate (SGS)). The select gates **208** may be horizontally divided (e.g., in the Y-direction) into multiple blocks **232** (e.g., corresponding to the blocks **137** (FIG. 1N)) horizontally separated (e.g., in the Y-direction) from one another by slots **230** (e.g., corresponding to the slot structures **165** (FIG. 1N)) including the support pillars **164** (FIG. 1N) and the third barrier material **138** (FIG. 1N) formed within the slot region **107** (FIG. 1N).

(147) Vertical conductive contacts **211** may electrically couple components to each other as shown. For example, the select lines **209** may be electrically coupled to the first select gates **208** and the interconnect lines **206** may be electrically coupled to the conductive structures **205**. The electronic device **200** may also include a control unit **212** (e.g., corresponding to the control unit **174** (FIG. 1N)) positioned under the memory array, which may include at least one of string driver circuitry, pass gates, circuitry for selecting gates, circuitry for selecting conductive lines (e.g., the data lines **202**, the interconnect lines **206**), circuitry for amplifying signals, and circuitry for sensing signals. The control unit **212** may be electrically coupled to the data lines **202**, the source tier **204**, the interconnect lines **206**, the first select gates **208**, and the second select gates **210**, for example. In some embodiments, the control unit **212** includes CMOS (complementary metal-oxide-semiconductor) circuitry. In such embodiments, the control unit **212** may be characterized as having a “CMOS under Array” (“CuA”) configuration.

(148) The first select gates **208** may extend horizontally in a first direction (e.g., the X-direction) and may be coupled to respective first groups of vertical strings **207** of memory cells **203** at a first end (e.g., an upper end) of the vertical strings **207**. The second select gate **210** may be formed in a

substantially planar configuration and may be coupled to the vertical strings **207** at a second, opposite end (e.g., a lower end) of the vertical strings **207** of memory cells **203**.

(149) The data lines **202** (e.g., digit lines, bit lines) may extend horizontally in a second direction (e.g., in the Y-direction) that is at an angle (e.g., perpendicular) to the first direction in which the first select gates **208** extend. Individual data lines **202** may be coupled to individual groups of the vertical strings **207** extending the second direction (e.g., the Y-direction) at the first end (e.g., the upper end) of the vertical strings **207** of the individual groups. Additional individual groups of the vertical strings **207** extending the first direction (e.g., the X-direction) and coupled to individual first select gates **208** may share a particular vertical string **207** thereof with individual group of vertical strings **207** coupled to an individual data line **202**. Thus, an individual vertical string **207** of memory cells **203** may be selected at an intersection of an individual first select gate **208** and an individual data line **202**. Accordingly, the first select gates **208** may be used for selecting memory cells **203** of the vertical strings **207** of memory cells **203**.

(150) The conductive structures **205** (e.g., word lines) may extend in respective horizontal planes. The conductive structures **205** may be stacked vertically, such that each conductive structure **205** is coupled to at least some of the vertical strings **207** of memory cells **203**, and the vertical strings **207** of the memory cells **203** extend vertically through the stack structure including the conductive structures **205**. The conductive structures **205** may be coupled to or may form control gates of the memory cells **203**.

(151) The first select gates **208** and the second select gates **210** may operate to select a vertical string **207** of the memory cells **203** interposed between data lines **202** and the source tier **204**. Thus, an individual memory cell **203** may be selected and electrically coupled to a data line **202** by operation of (e.g., by selecting) the appropriate first select gate **208**, second select gate **210**, and conductive structure **205** that are coupled to the particular memory cell **203**.

(152) The staircase structure **220** may be configured to provide electrical connection between the interconnect lines **206** and the conductive structures **205** through the vertical conductive contacts **211**. In other words, an individual conductive structure **205** may be selected via an interconnect line **206** in electrical communication with a respective vertical conductive contact **211** in electrical communication with the conductive structure **205**. The data lines **202** may be electrically coupled to the vertical strings **207** through conductive contact structures **234** (e.g., corresponding to the conductive contacts **160** (FIG. 1N)).

(153) Accordingly, in at least some embodiments, a memory device comprises a stack structure comprising alternating conductive structures and insulative structures arranged in tiers. Each of the tiers individually comprise a conductive structure and an insulative structure including at least one air gap separating vertically neighboring conductive structures. The memory device comprises strings of memory cells extending vertically through the stack structure within memory array regions, and support pillars extending vertically through the stack structure within slot regions separating the memory array regions. The support pillars comprise a liner material laterally adjacent to the at least one air gap. The memory device comprises a barrier material within the slot regions and laterally adjacent to the support pillars.

(154) Electronic devices (e.g., the electronic devices **100**, **200**) including the support pillars **164** and the third barrier material **138** of the slot structures **165** within the slot region **107**, according to embodiments of the disclosure, may be used in embodiments of electronic systems of the disclosure. For example, FIG. 3 is a block diagram of an electronic system **303**, in accordance with embodiments of the disclosure. The electronic system **303** may comprise, for example, a computer or computer hardware component, a server or other networking hardware component, a cellular telephone, a digital camera, a personal digital assistant (PDA), portable media (e.g., music) player, a Wi-Fi or cellular-enabled tablet such as, for example, an iPad® or SURFACE® tablet, an electronic book, a navigation device, etc. The electronic system **303** includes at least one memory device **305**. The memory device **305** may include, for example, an embodiment of an electronic

device previously described herein (e.g., the electronic devices **100**, **200** previously described with reference to FIGS. **1A** through **1P** and FIG. **2**) including the support pillars **164** and the third barrier material **138** of the slot structures **165** within the slot region **107**.

(155) The electronic system **303** may further include at least one electronic signal processor device **307** (often referred to as a “microprocessor”). The electronic signal processor device **307** may optionally include an embodiment of an electronic device previously described herein (e.g., one or more of the electronic devices **100**, **200** previously described with reference to FIGS. **1A** through **1P** and FIG. **2**). The electronic system **303** may further include one or more input devices **309** for inputting information into the electronic system **303** by a user, such as, for example, a mouse or other pointing device, a keyboard, a touchpad, a button, or a control panel. The electronic system **303** may further include one or more output devices **311** for outputting information (e.g., visual or audio output) to a user such as, for example, a monitor, a display, a printer, an audio output jack, a speaker, etc. In some embodiments, the input device **309** and the output device **311** may comprise a single touchscreen device that can be used both to input information to the electronic system **303** and to output visual information to a user. The input device **309** and the output device **311** may communicate electrically with one or more of the memory device **305** and the electronic signal processor device **307**.

(156) With reference to FIG. **4**, depicted is a processor-based system **400**. The processor-based system **400** may include various electronic devices (e.g., the electronic devices **100**, **200**) manufactured in accordance with embodiments of the present disclosure. The processor-based system **400** may be any of a variety of types such as a computer, pager, cellular phone, personal organizer, control circuit, or other electronic device. The processor-based system **400** may include one or more processors **402**, such as a microprocessor, to control the processing of system functions and requests in the processor-based system **400**. The processor **402** and other subcomponents of the processor-based system **400** may include electronic devices (e.g., the electronic devices **100**, **200**) manufactured in accordance with embodiments of the present disclosure.

(157) The processor-based system **400** may include a power supply **404** in operable communication with the processor **402**. For example, if the processor-based system **400** is a portable system, the power supply **404** may include one or more of a fuel cell, a power scavenging device, permanent batteries, replaceable batteries, and rechargeable batteries. The power supply **404** may also include an AC adapter; therefore, the processor-based system **400** may be plugged into a wall outlet, for example. The power supply **404** may also include a DC adapter such that the processor-based system **400** may be plugged into a vehicle cigarette lighter or a vehicle power port, for example.

(158) Various other devices may be coupled to the processor **402** depending on the functions that the processor-based system **400** performs. For example, a user interface **406** may be coupled to the processor **402**. The user interface **406** may include input devices such as buttons, switches, a keyboard, a light pen, a mouse, a digitizer and stylus, a touch screen, a voice recognition system, a microphone, or a combination thereof. A display **408** may also be coupled to the processor **402**. The display **408** may include an LCD display, an SED display, a CRT display, a DLP display, a plasma display, an OLED display, an LED display, a three-dimensional projection, an audio display, or a combination thereof. Furthermore, an RF sub-system/baseband processor **410** may also be coupled to the processor **402**. The RF sub-system/baseband processor **410** may include an antenna that is coupled to an RF receiver and to an RF transmitter (not shown). A communication port **412**, or more than one communication port **412**, may also be coupled to the processor **402**. The communication port **412** may be adapted to be coupled to one or more peripheral devices **414**, such as a modem, a printer, a computer, a scanner, or a camera, or to a network, such as a local area network, remote area network, intranet, or the Internet, for example.

(159) The processor **402** may control the processor-based system **400** by implementing software programs stored in the memory. The software programs may include an operating system, database

software, drafting software, word processing software, media editing software, or media playing software, for example. The memory is operably coupled to the processor **402** to store and facilitate execution of various programs. For example, the processor **402** may be coupled to system memory **416**, which may include one or more of spin torque transfer magnetic random access memory (STT-MRAM), magnetic random access memory (MRAM), dynamic random access memory (DRAM), static random access memory (SRAM), racetrack memory, and other known memory types. The system memory **416** may include volatile memory, non-volatile memory, or a combination thereof. The system memory **416** is typically large so that it can store dynamically loaded applications and data. In some embodiments, the system memory **416** may include semiconductor devices, such as the electronic devices (e.g., the electronic devices **100**, **200**) described above, or a combination thereof.

(160) The processor **402** may also be coupled to non-volatile memory **418**, which is not to suggest that system memory **416** is necessarily volatile. The non-volatile memory **418** may include one or more of STT-MRAM, MRAM, read-only memory (ROM) such as an EPROM, resistive read-only memory (RRAM), and flash memory to be used in conjunction with the system memory **416**. The size of the non-volatile memory **418** is typically selected to be just large enough to store any necessary operating system, application programs, and fixed data. Additionally, the non-volatile memory **418** may include a high-capacity memory such as disk drive memory, such as a hybrid-drive including resistive memory or other types of non-volatile solid-state memory, for example. The non-volatile memory **418** may include electronic devices, such as the electronic devices (e.g., the electronic devices **100**, **200**) described above, or a combination thereof.

(161) Accordingly, in at least some embodiments, a system comprises a processor operably coupled to an input device and an output device, and one or more electronic devices operably coupled to the processor. The one or more electronic devices comprise strings of memory cells extending vertically through a stack comprising a vertically alternating sequence of insulative structures and conductive structures, and slot structures extending vertically through the stack and separating the stack into blocks. Each block comprises some of the strings of memory cells. The one or more electronic devices comprise support structures laterally neighboring the strings of memory cells and located within the slot structures. The support structures are in electrical communication with the strings of memory cells and circuitry underlying the stack.

(162) The electronic devices and systems of the disclosure advantageously facilitate one or more of improved simplicity, greater packaging density, and increased miniaturization of components as compared to conventional devices and conventional systems. The methods of the disclosure facilitate the formation of devices (e.g., apparatuses, microelectronic devices, memory devices) and systems (e.g., electronic systems) having one or more of improved performance, reliability, and durability, lower costs, increased yield, increased miniaturization of components, improved pattern quality, and greater packaging density as compared to conventional devices (e.g., conventional apparatuses, conventional electronic devices, conventional memory devices) and conventional systems (e.g., conventional electronic systems).

(163) While certain illustrative embodiments have been described in connection with the figures, those of ordinary skill in the art will recognize and appreciate that embodiments encompassed by the disclosure are not limited to those embodiments explicitly shown and described herein. Rather, many additions, deletions, and modifications to the embodiments described herein may be made without departing from the scope of embodiments encompassed by the disclosure, such as those hereinafter claimed, including legal equivalents. In addition, features from one disclosed embodiment may be combined with features of another disclosed embodiment while still being encompassed within the scope of the disclosure.

## Claims

1. An electronic device, comprising: a stack comprising tiers of alternating conductive levels and insulative levels overlying a source; slots extending vertically through the stack and dividing the stack into blocks; support pillars within the slots and extending vertically through the stack, the support pillars exhibiting a lateral dimension in a first horizontal direction relatively larger than a lateral dimension of the slots in the first horizontal direction, substantially orthogonal to a second horizontal direction in which the slots extend; and a barrier material divided into discrete structures by the support pillars, the discrete structures of the barrier material within the slots and laterally separating the support pillars from one another in the second horizontal direction, a single line of the support pillars extending in the second horizontal direction within the slots, and the discrete structures of the barrier material extending between adjacent support pillars in the second horizontal direction.
2. The electronic device of claim 1, wherein the barrier material comprises one or more of silicon carbon nitride, polysilicon, tungsten, titanium, titanium nitride, and aluminum oxide.
3. The electronic device of claim 1, further comprising memory pillars within an array region of the electronic device and laterally adjacent to the slots, wherein the lateral dimension of the support pillars in the first horizontal direction is relatively larger than a lateral dimension of the memory pillars in the first horizontal direction.
4. The electronic device of claim 1, further comprising a carbon-containing material between the source and the stack, the support pillars extending through the carbon-containing material and contacting the source.
5. The electronic device of claim 1, wherein the insulative levels comprise air gaps vertically separating conductive structures of the conductive levels from one another, the insulative levels being substantially devoid of an oxide material within horizontal boundaries of the conductive structures.
6. The electronic device of claim 5, wherein the support pillars comprise a conductive material substantially surrounded by an insulative liner material, the air gaps partially defined by sidewalls of the insulative liner material of the support pillars.
7. A memory device, comprising: a stack structure comprising alternating conductive structures and insulative structures arranged in tiers, each of the tiers individually comprising a conductive structure and an insulative structure including at least one air gap separating vertically neighboring conductive structures; strings of memory cells extending vertically through the stack structure within memory array regions of the memory device; support pillars extending vertically through the stack structure within slot regions separating the memory array regions, the support pillars comprising a liner material laterally adjacent to the at least one air gap; and a barrier material within the slot regions and laterally adjacent to the support pillars, the barrier material divided into discrete structures by the support pillars.
8. The memory device of claim 7, further comprising conductive contacts and a CMOS under array (CUA) region under the memory array regions, wherein the conductive contacts connect the support pillars to circuitry of the CUA region.
9. The memory device of claim 7, further comprising an etch stop material underlying the barrier material within the slot regions.
10. The memory device of claim 7, wherein the support pillars individually exhibit a substantially circular cross-sectional shape, the support pillars laterally separated from one another by the barrier material along a vertical height of the support pillars.
11. The memory device of claim 7, further comprising a carbon-containing material overlying the stack structure, wherein upper surfaces of the carbon-containing material, the barrier material, and the support pillars are substantially coplanar with one another, and wherein the support pillars extend to a lower depth than a depth to which the barrier material extends.
12. A method of forming an electronic device, the method comprising: forming pillars in a stack

comprising alternating first materials and second materials within an array region, the stack overlying a source; forming slots extending vertically through the stack and dividing the stack into blocks; forming a barrier material within the slots; forming support pillar openings through the barrier material; replacing the first materials of the stack with one or more conductive materials through the support pillar openings to form tiers of the stack comprising alternating conductive materials and the second materials; and forming support pillars within the support pillar openings and extending vertically through the stack, the support pillars exhibiting a lateral dimension in a first horizontal direction relatively larger than a lateral dimension of the slots in the first horizontal direction, substantially orthogonal to a second horizontal direction in which the slots extend, a single line of the support pillars extending in the second horizontal direction within the slots, the barrier material divided into discrete structures by the support pillars, the discrete structures of the barrier material laterally separating the support pillars from one another in the second horizontal direction, and the discrete structures of the barrier material extending between adjacent support pillars in the second horizontal direction.

13. The method of claim 12, wherein forming the pillars in the stack comprises: forming a sacrificial material in openings extending vertically through a first deck; forming a second deck over the first deck; forming extended openings extending vertically through the first deck and the second deck; and forming the pillars in the extended openings.

14. The method of claim 12, wherein forming the slots comprises forming additional sacrificial material in a lower portion of the slots prior to forming the pillars and forming extended slots extending vertically through an entirety of the stack following formation of the pillars.

15. The method of claim 1, further comprising: removing the second materials of the stack to form openings extending between vertically neighboring conductive structures; and forming a liner material within the slots to form air gaps within the openings, lateral side boundaries of the air gaps substantially vertically aligned with lateral side surfaces of at least some of the conductive structures.

16. The method of claim 12, wherein forming the support pillars comprises electrically connecting a conductive material of the support pillars to conductive structures underlying the stack.

17. The method of claim 12, further comprising forming an additional barrier material over the source prior to forming the stack, a material composition of the additional barrier material substantially the same as a material composition of the barrier material within the slots.

18. The method of claim 12, further comprising forming additional discrete structures of the barrier material in additional support pillar openings within the array region during formation of the barrier material within the slots.

19. A system, comprising: a processor operably coupled to an input device and an output device; and one or more electronic devices operably coupled to the processor, the one or more electronic devices comprising: strings of memory cells extending vertically through a stack comprising a vertically alternating sequence of insulative structures and conductive structures; slot structures extending vertically through the stack and separating the stack into blocks, each block comprising some of the strings of memory cells; support structures laterally neighboring the strings of memory cells and located within the slot structures, the support structures in electrical communication with the strings of memory cells and circuitry underlying the stack; and a barrier material within the slots and laterally separating the support structures from one another, the barrier material divided into discrete structures by the support structures.

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